

# **Oxide-Semiconductor Materials for Quantum Computation**

***Jeremy Levy***

***North American Molecular Beam Epitaxy  
Conference (NA-MBE)***

***Keystone, CO***

***2 October 2003***



# Outline

- Introduction to quantum computation
- COSMQC architecture
- Selected results
- Future directions



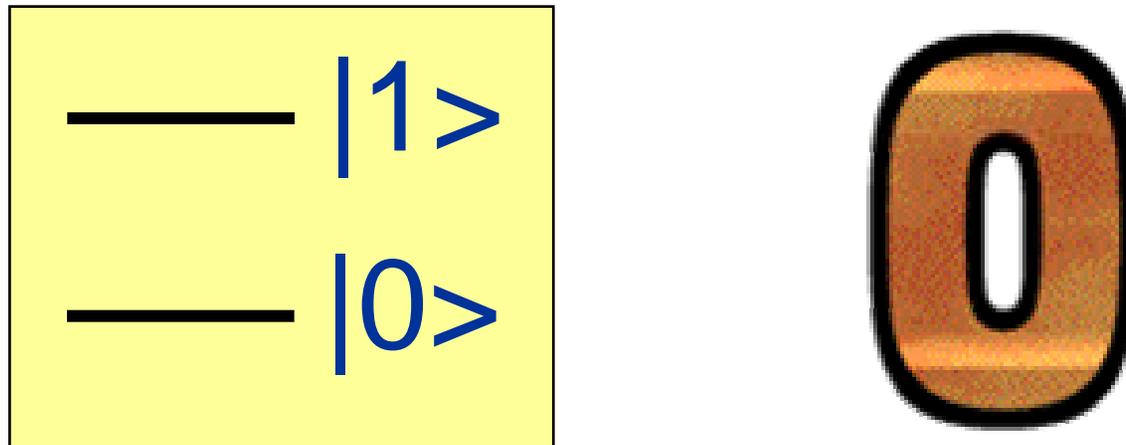
# What is a Quantum Computer?

- A quantum computer processes quantum information



# What is quantum information?

- Quantum information is stored in quantum bits (qubits)



Qubit can be in a quantum superposition of  $|0\rangle$  and  $|1\rangle$



# What can quantum computers do?

- Quantum computers can factor numbers exponentially faster than classical computers (Shor, 1994)

Difficulty of factoring numbers is foundation of public key encryption

114381625757888867669235  
779976146612010218296721  
242362562561842935706935  
245733897830597123563958  
705058989075147599290026  
879543541

=

349052951084765094914784  
961990389813341776463849  
3387843990820577

X

327691329932667095499619  
881908344614131776429679  
92942539798288533



Why are quantum computers  
so much faster?



# Qubit Phase Space

—  $|1\rangle$   
—  $|0\rangle$

- A single qubit exists in a 2-dimensional space

$$|\psi\rangle = a_0|0\rangle + a_1|1\rangle, \quad |a_0|^2 + |a_1|^2 = 1$$



# Qubit Phase Space

—  $|1\rangle$   
—  $|0\rangle$

- A single qubit exists in a 2-dimensional space

$$|\psi\rangle = a_0 |0\rangle + a_1 |1\rangle, \quad |a_0|^2 + |a_1|^2 = 1$$

- For  $n$ -qubit system,  $2^n$  complex numbers required

$$|\Psi\rangle = a_0 |\underbrace{000\dots 000}_n\rangle + a_1 |000\dots 001\rangle + a_2 |000\dots 010\rangle + \dots + a_{2^n-1} |111\dots 111\rangle$$

A state with  $n=100$  qubits is specified by  $2^{100} \cong 10^{30}$  coefficients !

A quantum program is specified by  $(2^{100})^2 \cong 10^{60}$  coefficients !!

(Final answer is a string of  $n$  classical bits)



# Quantum Information Science and Technology Roadmap

December 1, 2002  
Version 1.0

## SOLID STATE QUANTUM COMPUTING Quantum dot and spin based

### TIME LINES.



This document is available electronically at: <http://qist.lanl.gov>

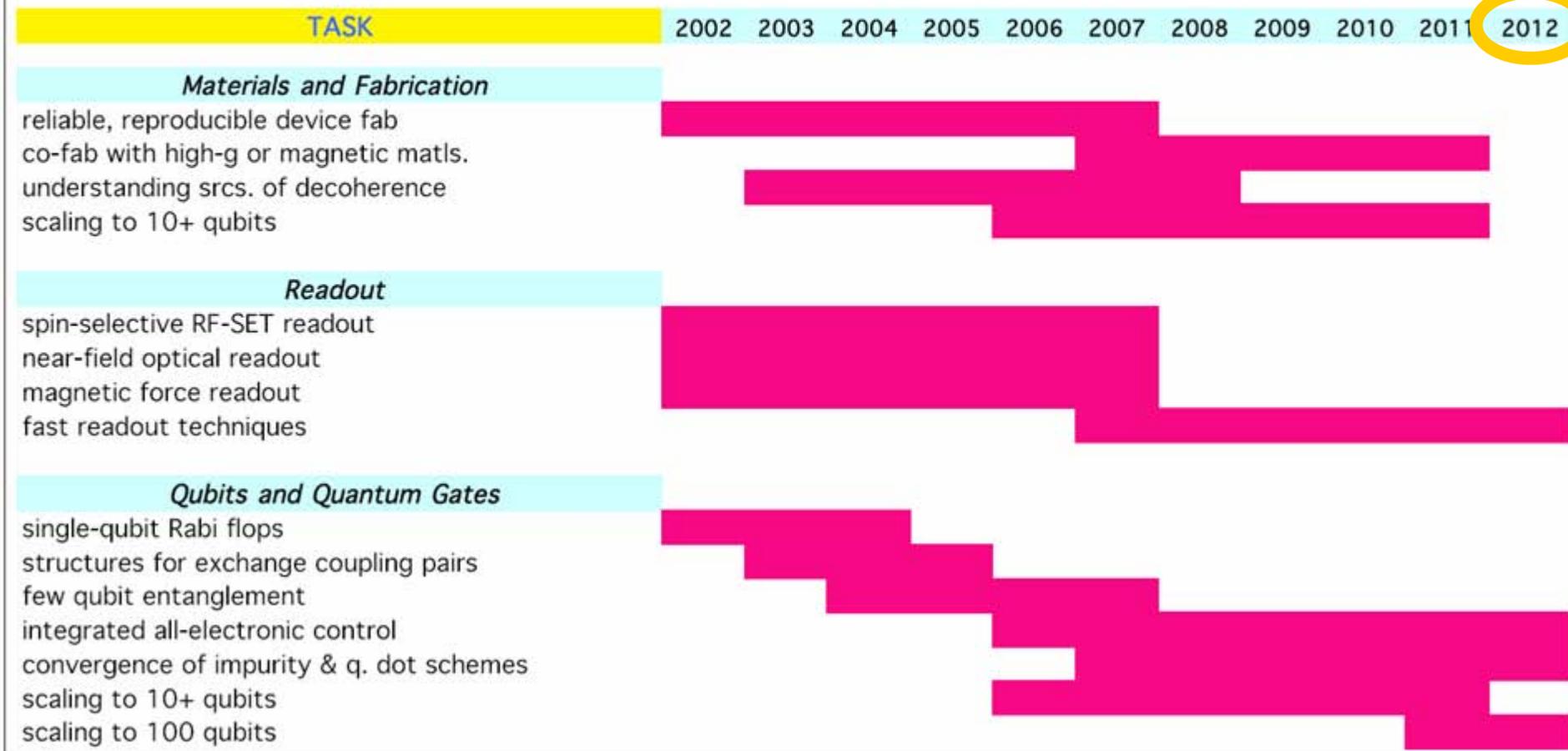


Figure 6-1. Solid state QC developmental timeline



Center for Oxide-Semiconductor Materials for Quantum Computation COSMQC

# Five Requirements for Quantum Computation

(D. P. Divincenzo, quant-ph/0002077)

Quantum Memory

Quantum CPU

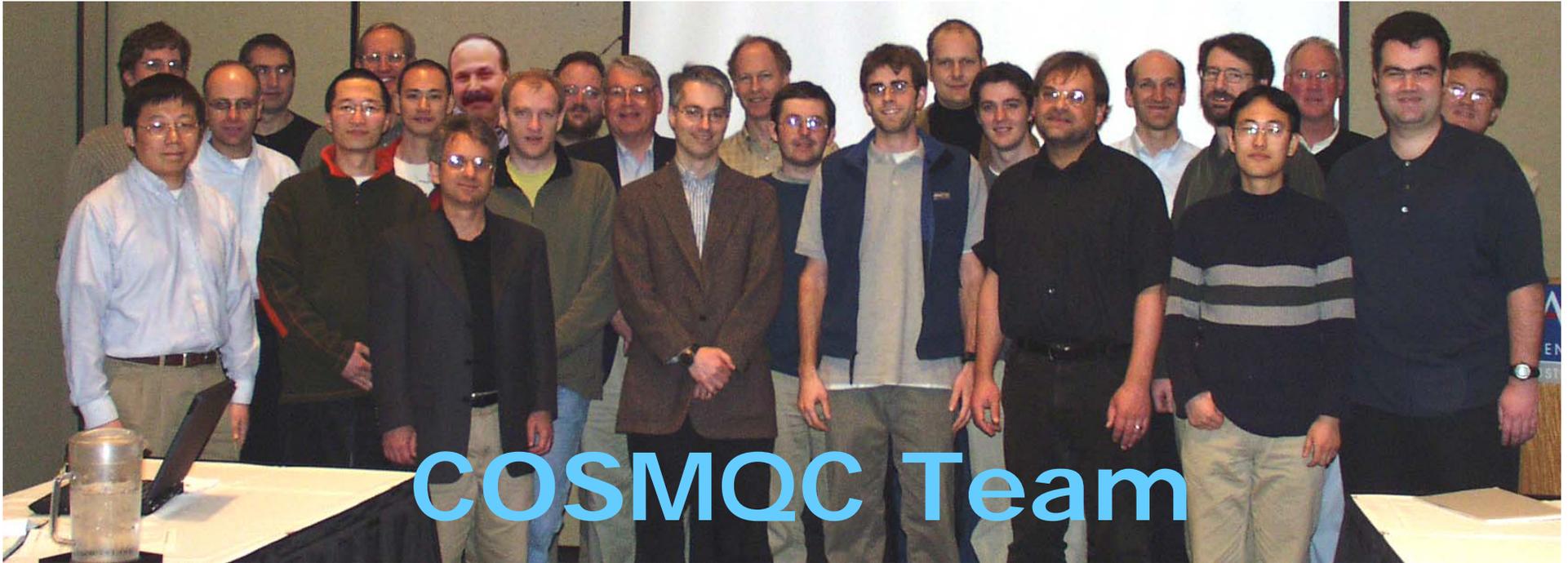
Quantum  
Coherence

Quantum  
Coherence



Quantum I/O





## Materials

- Darrell G. Schlom (Penn State U.)
  - » Venugopalan Vaithyanathan
  - » Lisa Edge
  - » Sven Clemens
- John T. Yates, Jr. (U. Pittsburgh)
  - » Olivier Guise
  - » Sergey Mezheny
  - » Hubertus Marbach
- Joachim Ahner (Seagate)
- Rodney A. McKee (ORNL)

## Experiments

- Jeremy Levy (Director, U. Pittsburgh)
  - » Petru Fodor
  - » Patrick Irvin
  - » Amlan Basak
  - » Ajay Kochhar
  - » Scott Rothenberger
- Keith Nelson (MIT)
  - » Joshua Vaughan
- David D. Awschalom (UCSB)
  - » Yuichiro Kato
- Bruce Kane (U. Maryland)
  - » Kenton Brown

- Principal Investigator
- Postdoc
- Graduate Student
- Undergraduate

## Theory

- Michael E. Flatté (U. Iowa)
  - » Craig Pryor
  - » Jian-Ming Tang
  - » Wayne Lau
  - » Zhi Gang Yu
  - » Ionel Tifrea
  - » Michael Leuenberger
  - » Ben Moehlmann
- Daniel Loss (U. Basel)
  - » Florian Meier
- C. Stephen Hellberg (NRL)
  - » Larry L. Boyer



# COSMQC architecture

J. Levy, Phys. Rev. A **64**, 052306 (2001).

## (R1) Qubit

- » Electron spin(s) localized near Ge QDs

## (R2) Initialization

- » Optical orientation in Ge quantum dots

## (R3) Long Coherence Times

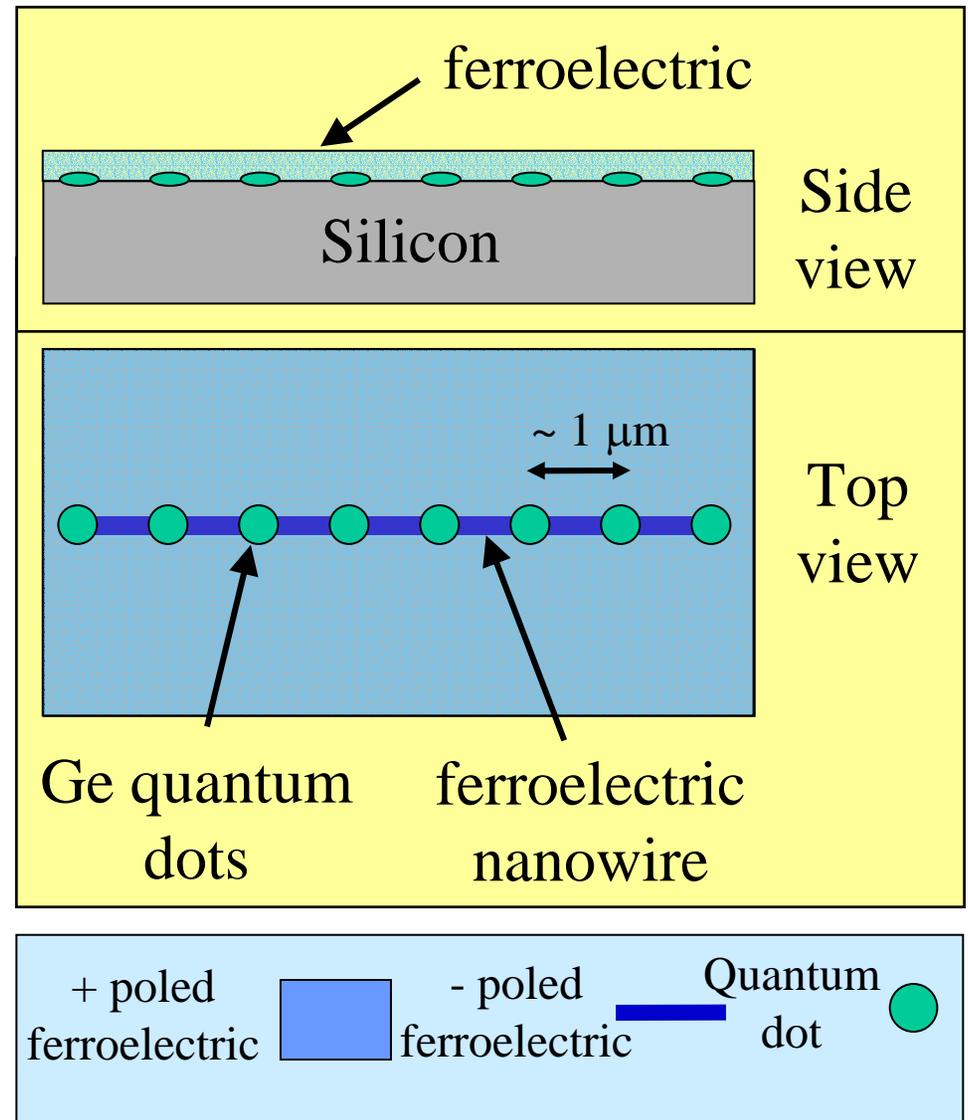
- »  $T_2 \sim \text{ms}$  for Si ;  $T_{\text{gate}} \sim \text{ps}$

## (R4) Gating

- » Ferroelectric coupling / optical rectification

## (R5) Readout

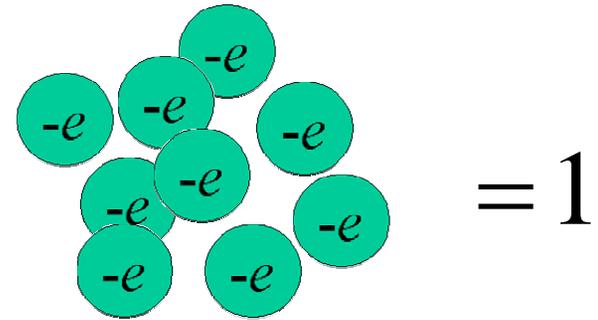
- » Optical (weak); SET (strong)



# Charge bits *vs.* spin qubits



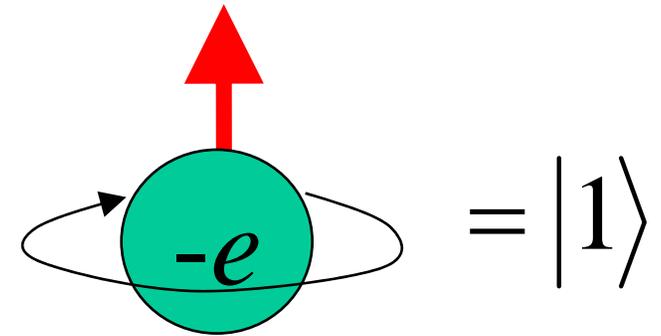
# Electron charge bits



Electronics:  $\Psi = \psi(\vec{r}) \cdot \chi_s$



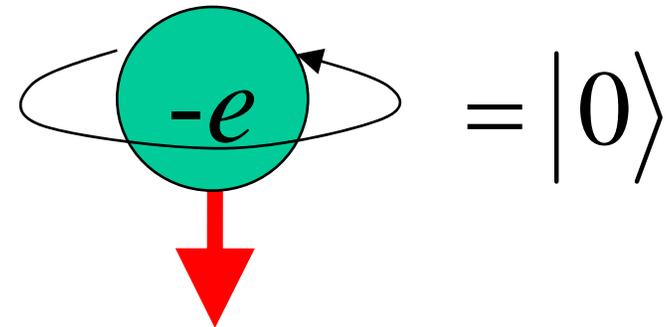
# Electron spin qubits



$$= |1\rangle$$

Spintronics:  $\Psi = \chi_s \cdot \psi(\vec{r})$

- Use ferroelectric to mediate spin interactions in semiconductors



$$= |0\rangle$$



# Ferroelectric Gating of Electron Spin

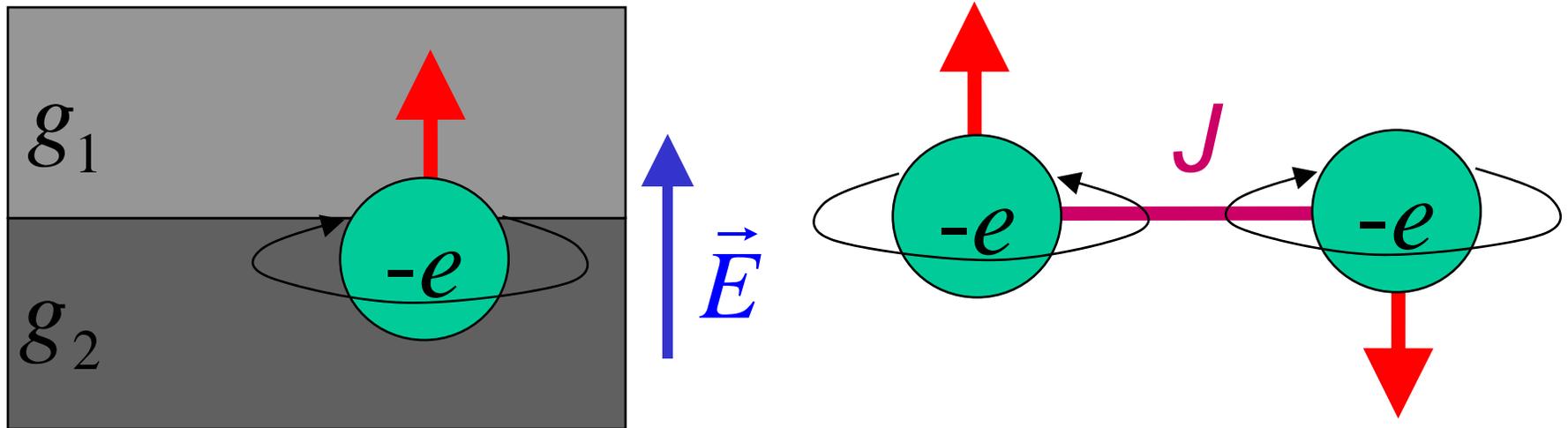
Ferroelectric enables fast, local optical control of electric fields

Zeeman one-qubit

Heisenberg two-qubit

$$H_Z = \mu_B \vec{s} \cdot \vec{g}(\vec{E}) \cdot \vec{B}$$

$$H_{ex} = J(\vec{E}) \vec{s}_1 \cdot \vec{s}_2$$

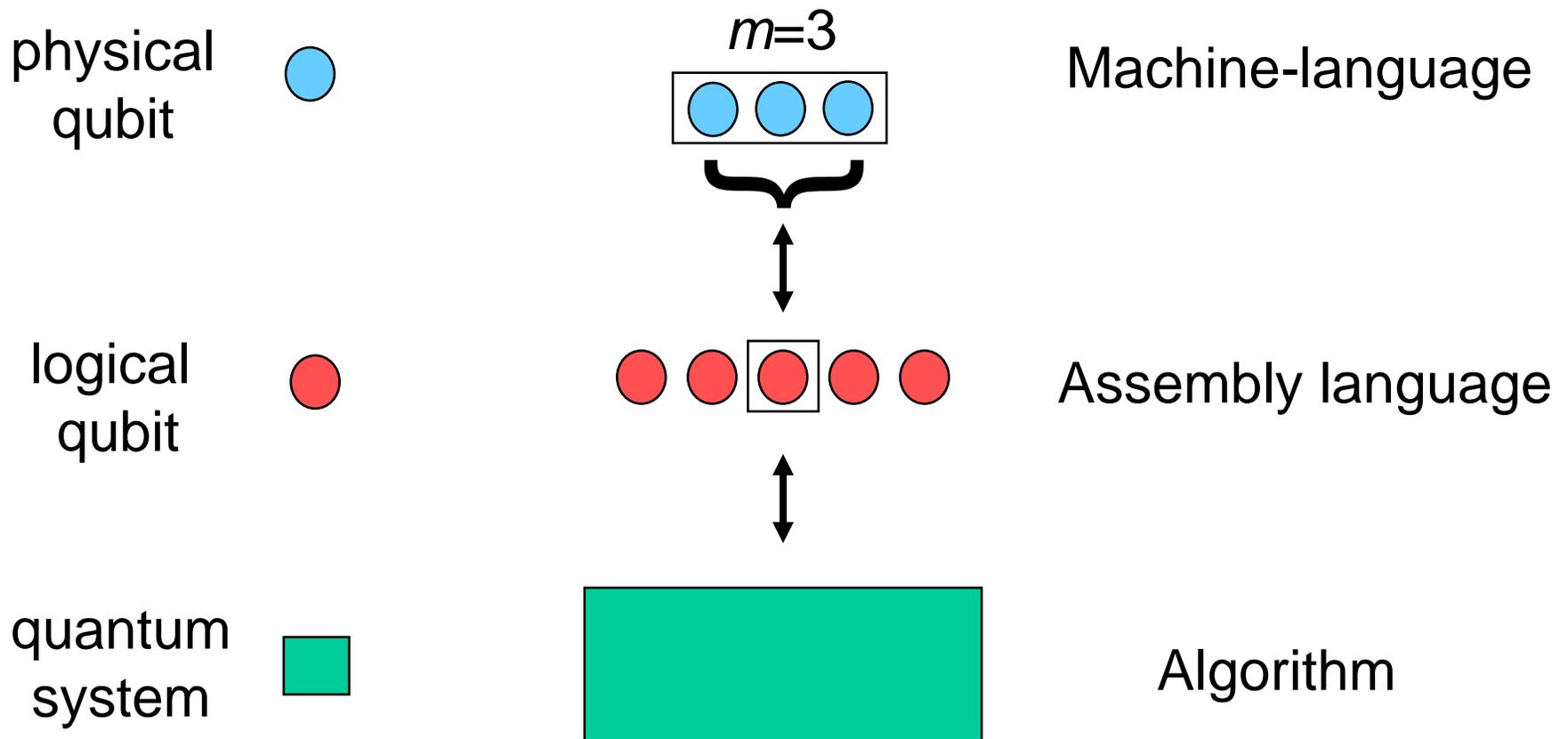


One-qubit and two-qubit gates sufficient for universal quantum computation



# Designer qubits

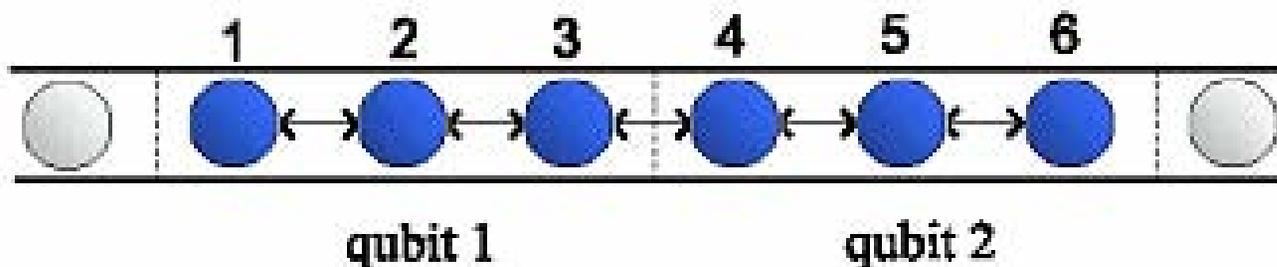
“Logical” qubit is formed from a 2-dimensional subspace of  $m$  “physical” qubits



# Designer qubits

- Example:  $m=3$

- DiVincenzo *et al.*, Nature **408**, 339 (2000).



- Heisenberg exchange interaction is *universal*
  - » 3-4 Heisenberg operations  $\leftrightarrow$  single qubit operation
  - » 19 Heisenberg operations  $\leftrightarrow$  cNOT operation

**1  $\ll$  2!**



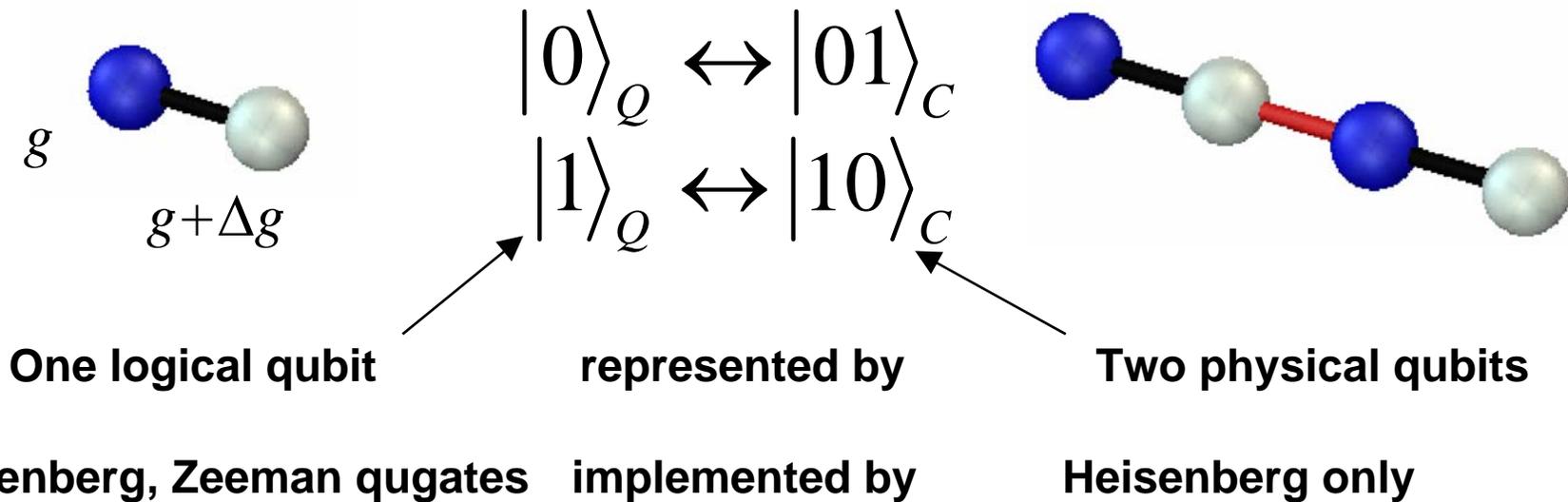
## Universal Quantum Computation with Spin-1/2 Pairs and Heisenberg Exchange

Jeremy Levy

*Center for Oxide-Semiconductor Materials for Quantum Computation, and Department of Physics and Astronomy, University of Pittsburgh, 3941 O'Hara Street, Pittsburgh, Pennsylvania 15260*

(Received 23 January 2001; published 17 September 2002)

An efficient and intuitive framework for universal quantum computation is presented that uses pairs of spin-1/2 particles to form logical qubits and a single physical interaction, Heisenberg exchange, to produce all gate operations. Only two Heisenberg gate operations are required to produce a controlled  $\pi$ -phase shift, compared to nineteen for exchange-only proposals employing three spins. Evolved from well-studied decoherence-free subspaces, this architecture inherits immunity from collective decoherence mechanisms. The simplicity and adaptability of this approach should make it attractive for spin-based quantum computing architectures.

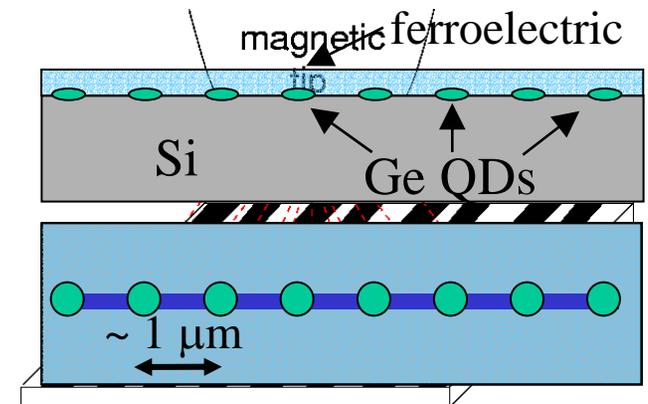


# Quantum computing with spin cluster qubits

Florian Meier, Jeremy Levy, and Daniel Loss, PRL 90, 047901 (2003)

- Design of spin-based qubits and qugates challenging
  - » Control over electron exchange, magnetic interactions
  - » Encoded qubits eliminate Zeeman, but still sensitive to internal structure

Loss and DiVincenzo, Phys Rev A 64, 022311, (2001) (1998).



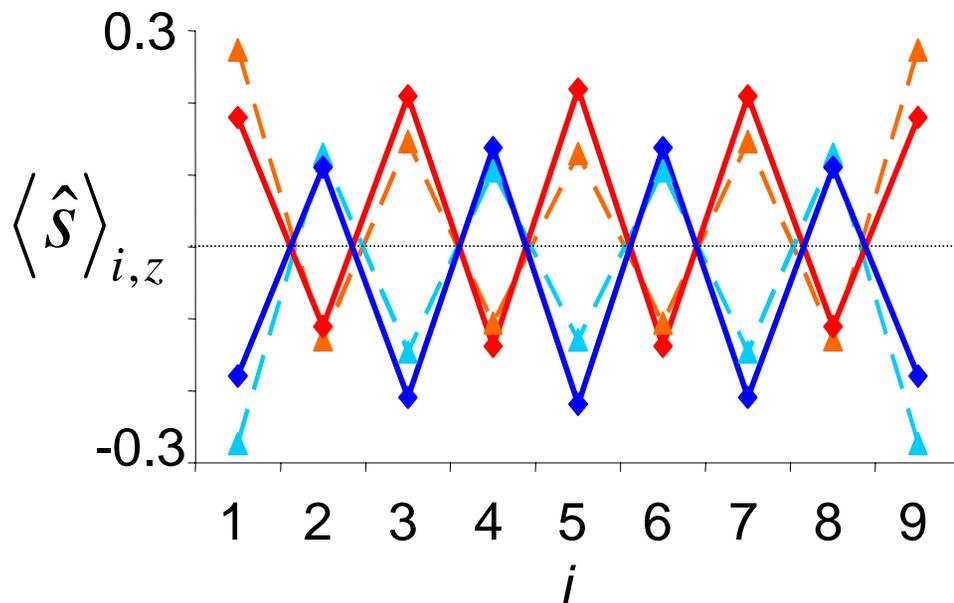
- Ideal “designer” qubit:
  - large compared compared to electron wavefunction
  - » insensitive to variations smaller than qubit



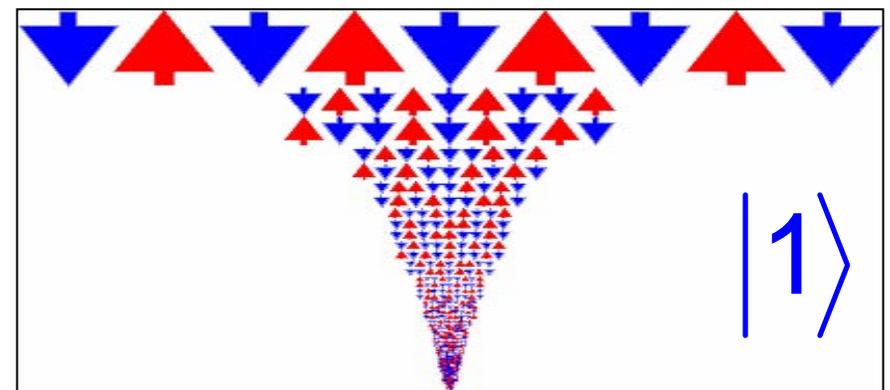
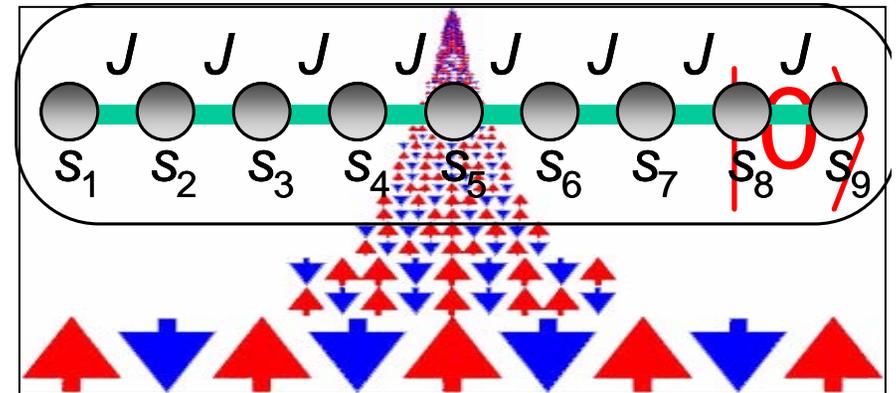
# Spin chains as qubits

Open spin chain with  $n_c$  sites:  
(e.g., neighboring QDs)

For  $n_c$  odd, ground state is  
doubly degenerate, with  $S_{\text{tot}}=1/2$

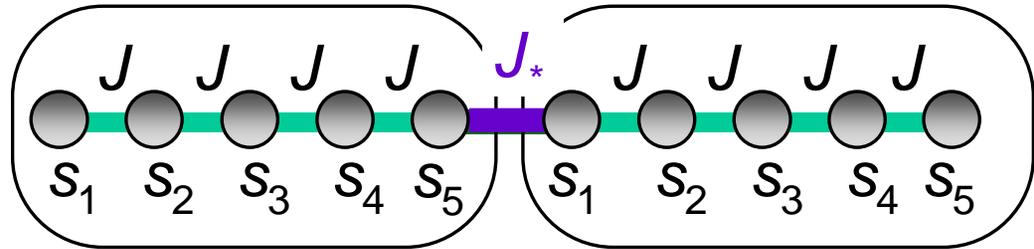


$$\hat{H} = J \sum_{i=1}^{n_c-1} \hat{S}_i \cdot \hat{S}_{i+1}$$



# Coupling Cluster Qubits

$$\hat{H}_* = J_*(t) \hat{S}_{n_c}^I \cdot \hat{S}_1^H$$

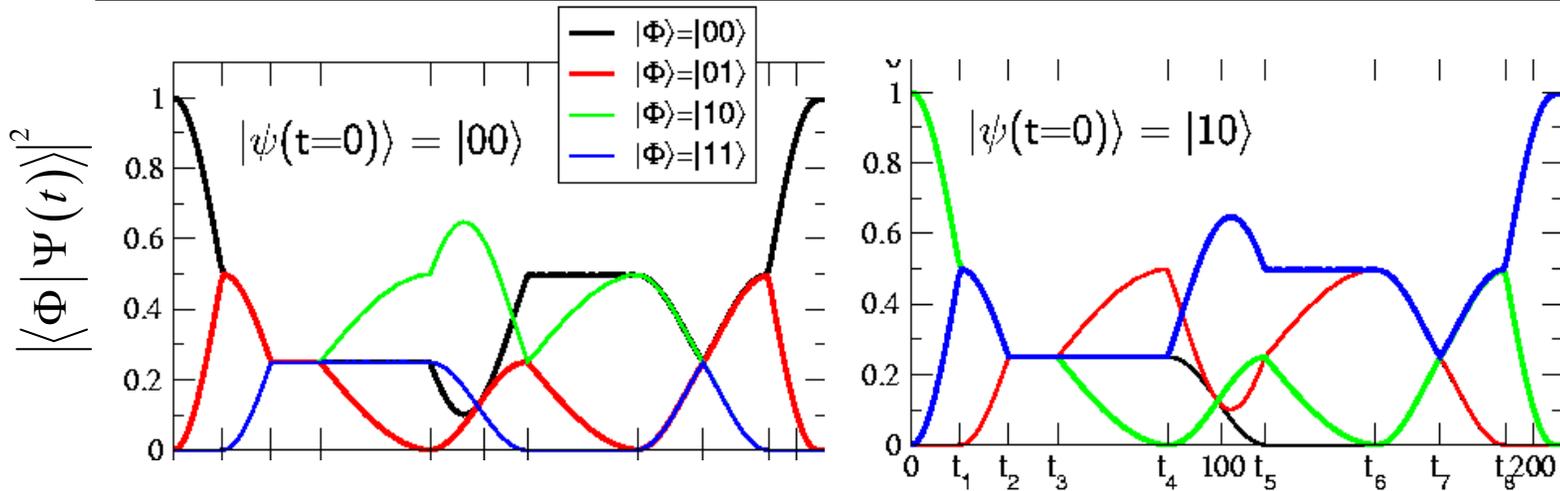


Effective Hamiltonian in basis  
 $\{|00\rangle, |01\rangle, |10\rangle, |11\rangle\}$ :

$$\hat{H}_* = \frac{J_*}{4} \left| \langle 0 | \hat{S}_{1,z} | 0 \rangle \right|^2 \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & -1 & 2 & 0 \\ 0 & 2 & -1 & 0 \\ 0 & 0 & 0 & 1 \end{pmatrix}$$

CNOT:

$$U_{CNOT} = e^{-i\pi S_y^H / 2} e^{i2\pi \mathbf{m}_1 \cdot \mathbf{S}^I / 3} e^{i2\pi \mathbf{m}_2 \cdot \mathbf{S}^H / 3} U_*(\pi/2) e^{i\pi S_y^H} U_*(\pi/2) e^{-i\pi S_x^I / 2} e^{-i\pi S_x^H / 2} e^{i\pi S_y^H / 2}$$



# Scaling of Decoherence

- Fluctuating fields and nuclear spins contribute to spin decoherence in semiconductors
  - » Magnetic moment of spin cluster qubit same as for single spin

- For spatially uniform (random) magnetic fields

$$\hat{H}_\phi^B = b(t) \sum_{i=1}^{n_c} \hat{S}_{i,z} \quad \langle b(t)b(0) \rangle = 2\pi\gamma^B \delta(t)$$

decoherence independent of  $n_c$

- For independent fluctuating fields

$$\hat{H}_\phi^B = \sum_{i=1}^{n_c} b_i(t) \hat{S}_{i,z} \quad \langle b_i(t)b_j(0) \rangle = 2\pi\gamma^B \delta(t) \delta_{ij}$$

decoherence proportional to  $n_c$



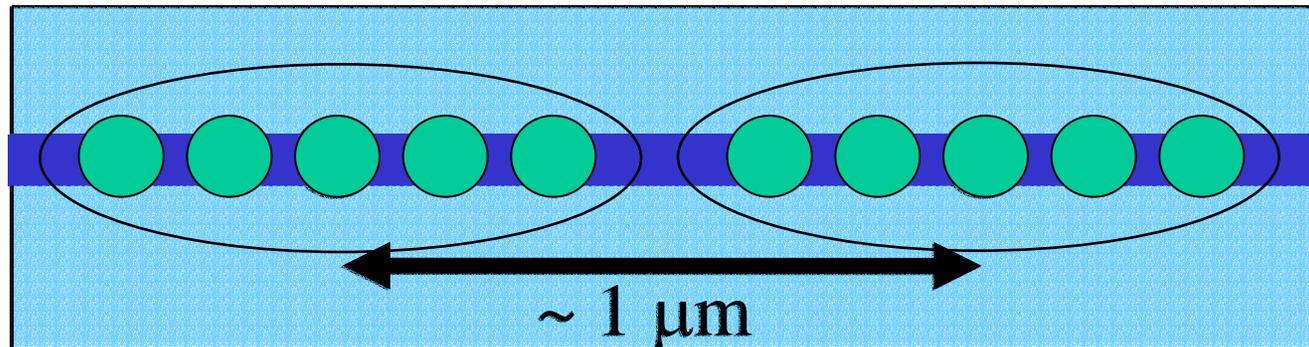
# Additional properties of spin cluster qubits

- Spin cluster qubit is robust against
  - » disorder
  - » topology of intra-cluster exchange
  - » symmetry of exchange (e.g., Heisenberg, XY)
- Significant advantage
  - » quantum computing possible **without local control** over spin interactions



# Applications to ferroelectrically coupled quantum dots

Original proposal<sup>1</sup> with spin cluster qubit



Improvement: electrons are localized

<sup>1</sup>J. Levy, Phys. Rev. A **64**, 52306 (2001).



# Physical Qugates

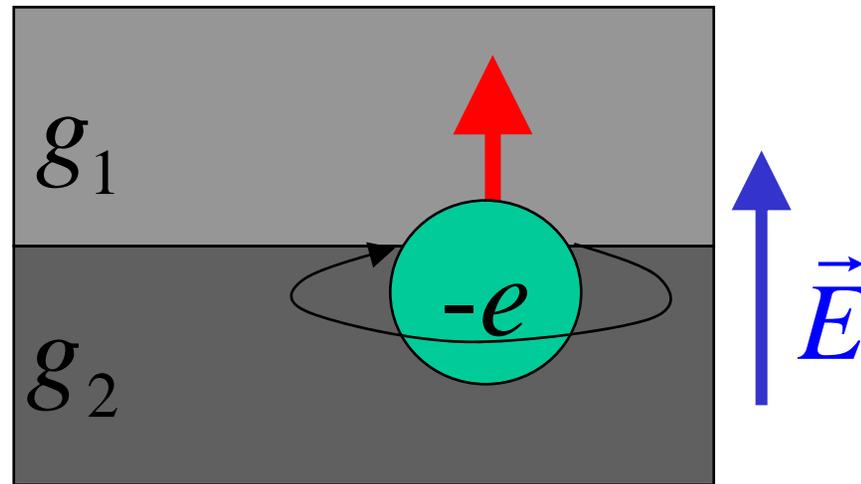


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# One-qubit gates

(voltage-controlled electron spin resonance)

$$H_Z = \mu_B \vec{s} \cdot \vec{g}(\vec{E}) \cdot \vec{B}$$



## Gigahertz Electron Spin Manipulation Using Voltage-Controlled g-Tensor Modulation

Y. Kato,<sup>1,2</sup> R. C. Myers,<sup>1</sup> D. C. Driscoll,<sup>1</sup> A. C. Gossard,<sup>1</sup> J. Levy,<sup>1,2</sup> D. D. Awschalom<sup>1,2\*</sup>

<sup>1</sup>Center for Spintronics and Quantum Computation, University of California, Santa Barbara, CA 93106. <sup>2</sup>Center for Oxide-Semiconductor Materials for Quantum Computation, University of Pittsburgh, Pittsburgh, PA 15260

\*To whom correspondence should be addressed. E-mail: awsch@physics.ucsb.edu

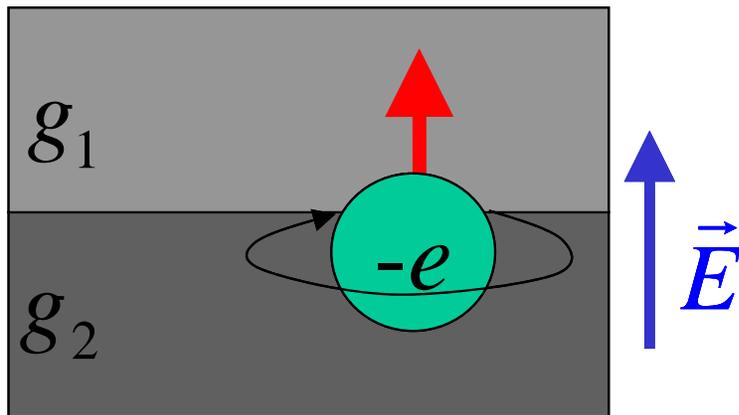
We present a scheme that enables gigahertz-bandwidth three-dimensional control of electron spins in a semiconductor heterostructure using a single voltage signal. Microwave modulation of the Landé g-tensor produces frequency-modulated electron spin precession. Driving at the Larmor frequency results in g-tensor modulation resonance, functionally equivalent to electron spin resonance but without the use of time-dependent magnetic fields. These results provide proof of concept that quantum spin information can be locally manipulated using high-speed electrical circuits.

Electron spin dynamics can be described by an effective Hamiltonian  $H(t) = (\mu_B / \hbar) \mathbf{S} \cdot \mathbf{g} \cdot \mathbf{B} \equiv \mathbf{S} \cdot \Omega(t)$ , where  $\mu_B$  is the Bohr magneton,  $\hbar$  is the Planck's constant,  $\mathbf{S}$  is the spin angular momentum operator,  $\mathbf{g}$  is the Landé g-tensor, and  $\mathbf{B}$  is the magnetic field. The Hamiltonian is conventionally separated into two terms  $H(t) = H_0 + H_1(t)$ , where  $H_0 = (\mu_B / \hbar) \mathbf{S} \cdot \mathbf{g} \cdot \mathbf{B}_0 \equiv \mathbf{S} \cdot \Omega_0$  is time-independent and  $H_1(t) = \mathbf{S} \cdot \Omega_1(t)$  governs spin dynamics in the rotating frame. The effect of  $\Omega_1(t)$  can be seen by resolving it into

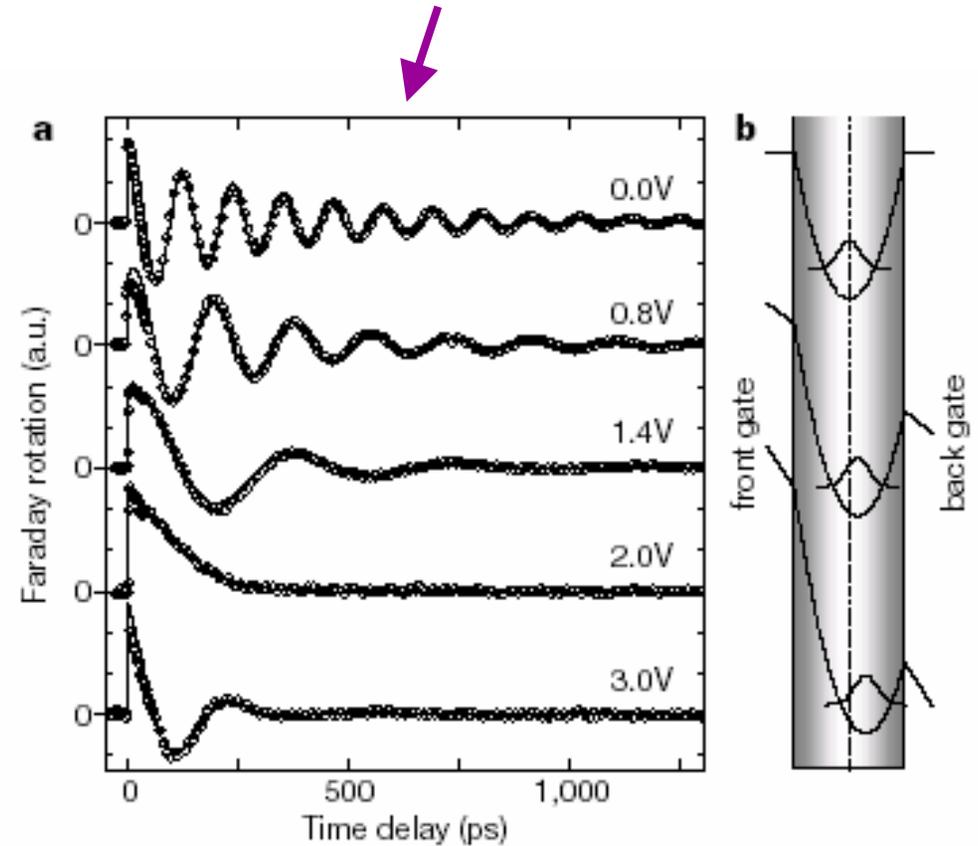


# Background: g-factor engineering

- g-factor tuning in a parabolic quantum well
  - » Electric field shifts electron into region of GaAs/AlGaAs with varying g-factor



## Optical detection of spin precession



G. Salis, Y. Kato, K. Ensslin, D. C. Driscoll, A. C. Gossard, and D. D. Awschalom, *Nature* **414**, 619 (2001).



# Exploiting g-Tensor Anisotropy

$$H(t) = (\mu_B / \hbar) \mathbf{S} \cdot \vec{\mathbf{g}} \cdot \mathbf{B} \equiv \mathbf{S} \cdot \Omega(t)$$

where  $\vec{\mathbf{g}} = \vec{\mathbf{g}}(V(t))$  and  $\mathbf{B}$  is static

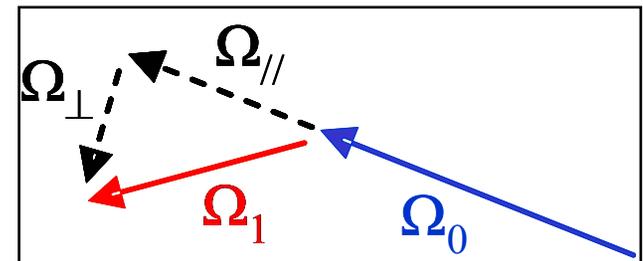
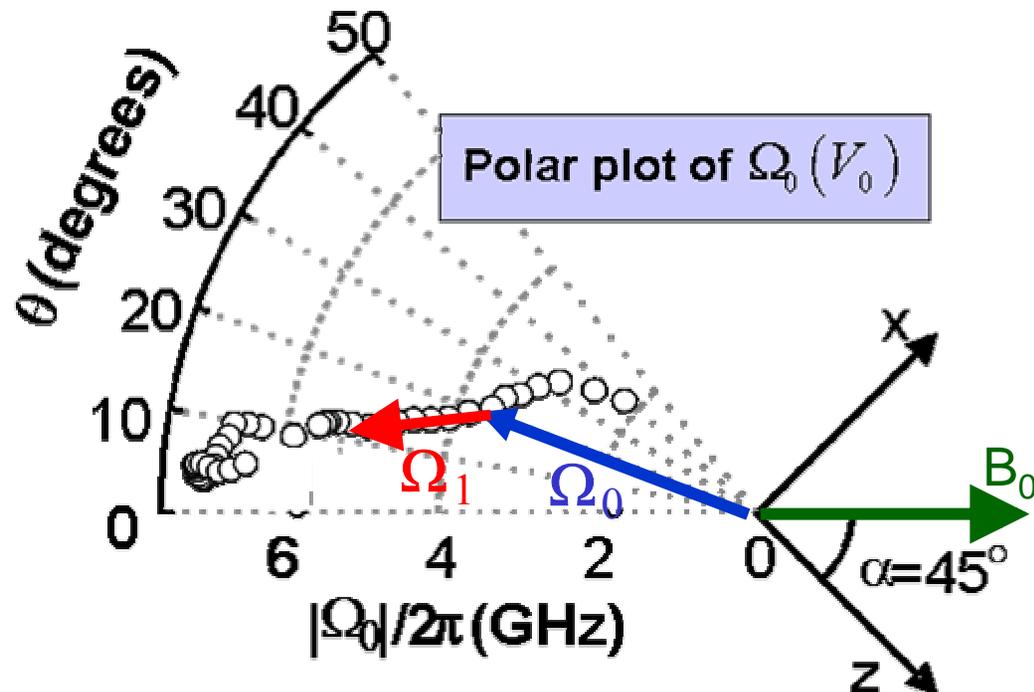
- **Precession vector  $\Omega$  is not always parallel to  $\mathbf{B}$** 
  - » Changes in magnitude of  $\Omega$  produce frequency-modulated spin precession
  - » Changes in direction of  $\Omega$  produce effective ESR



# g-Tensor Modulation

$$\mathbf{\Omega}_0(V_0) = \begin{pmatrix} \Omega_{0x} \\ \Omega_{0z} \end{pmatrix} = \frac{\mu_B}{\hbar} \begin{pmatrix} g_{90}(V_0) & 0 \\ 0 & g_0(V_0) \end{pmatrix} \cdot \begin{pmatrix} B_0 \sin \alpha \\ B_0 \cos \alpha \end{pmatrix} = \frac{\mu_B}{\hbar} B_0 \begin{pmatrix} g_{90}(V_0) \sin \alpha \\ g_0(V_0) \cos \alpha \end{pmatrix}$$

$$V(t) = V_0 + V_1(t) \longrightarrow \mathbf{\Omega}(t) = \mathbf{\Omega}_0 + \mathbf{\Omega}_1(t)$$



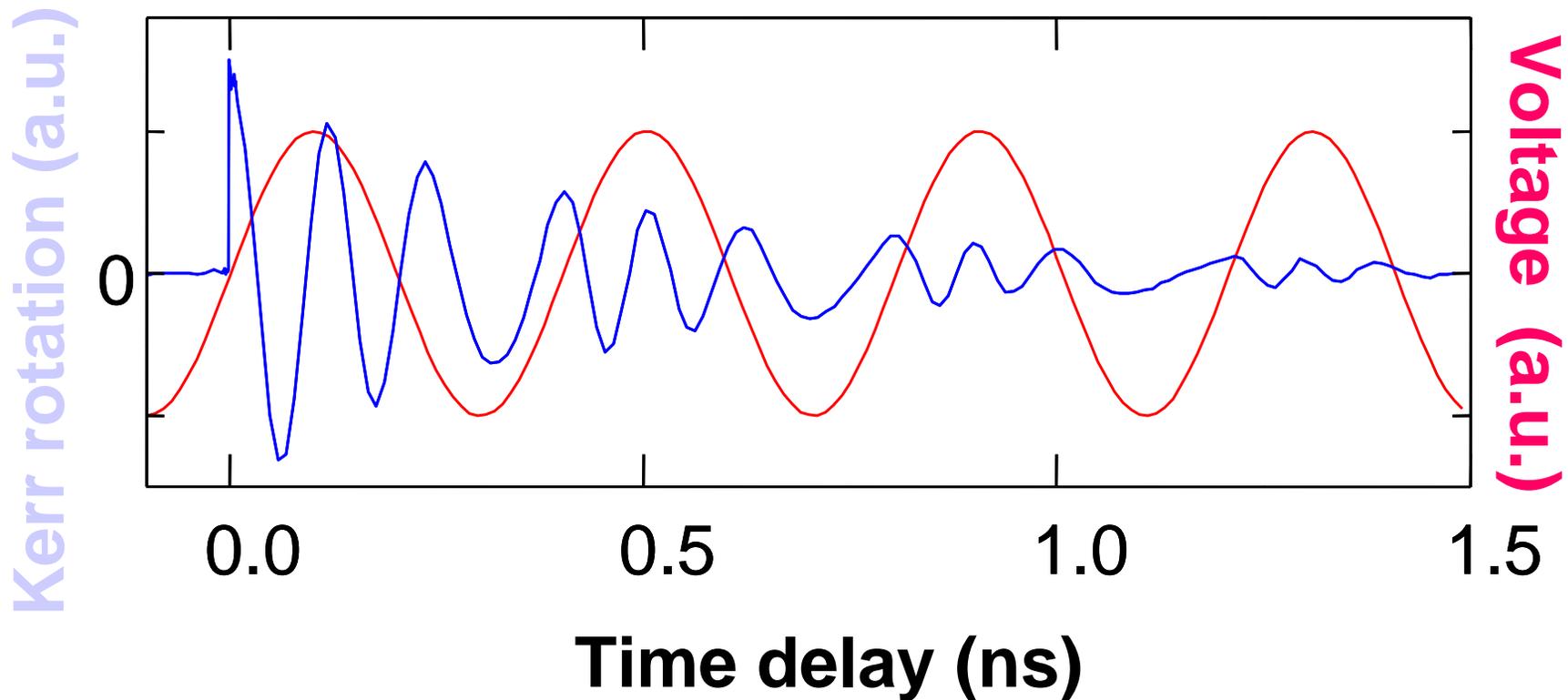
$$\mathbf{\Omega}_1(t) = \mathbf{\Omega}_{||}(t) + \mathbf{\Omega}_{\perp}(t)$$



# Frequency-Modulated Spin Precession

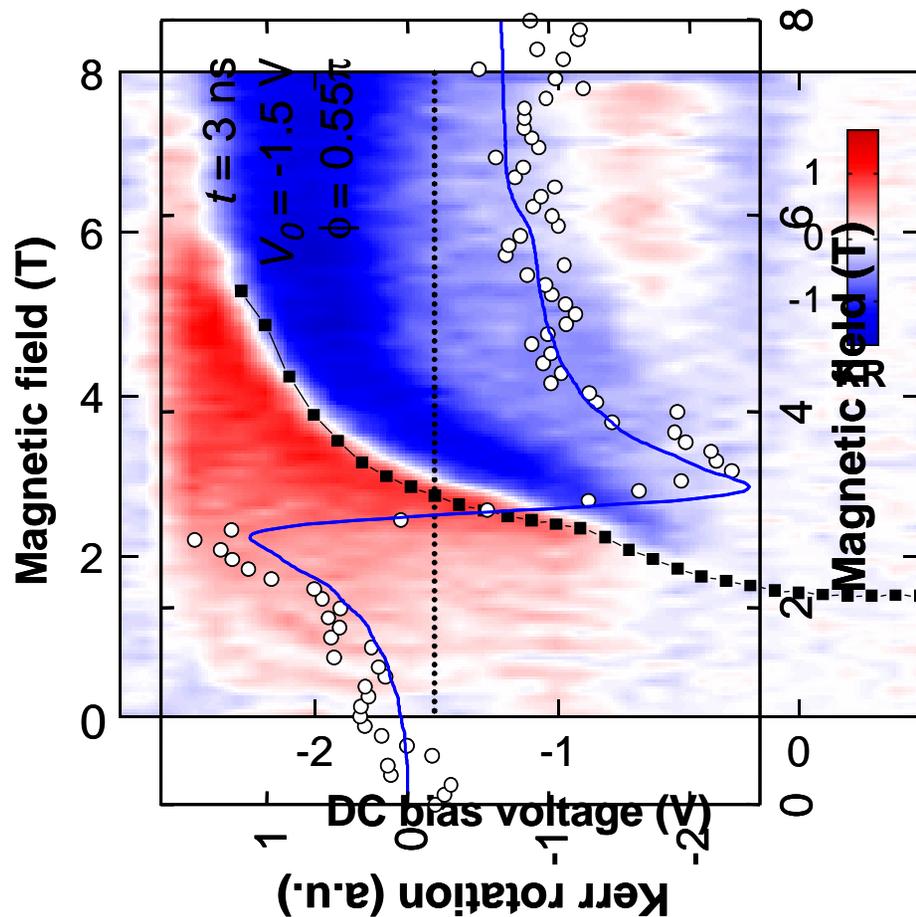
$$\mathbf{\Omega}_1(t) = \mathbf{\Omega}_{\parallel}(t) + \mathbf{\Omega}_{\perp}(t)$$

- Electrical “pump” (red) modulates electron spin precession (blue) at GHz frequencies



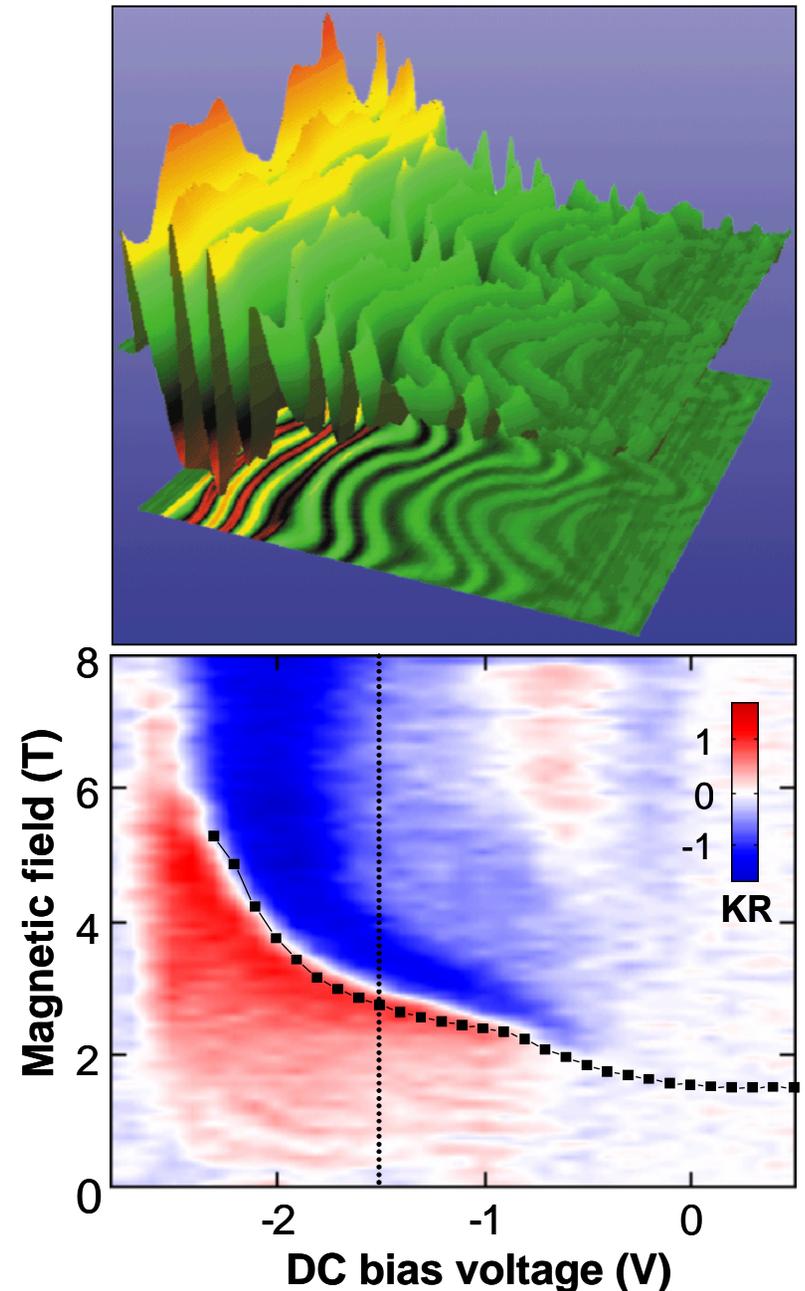
# g-Tensor Modulation Resonance

$$\boldsymbol{\Omega}_1(t) = \boldsymbol{\Omega}_{\parallel}(t) + \boldsymbol{\Omega}_{\perp}(t)$$



# Discussion

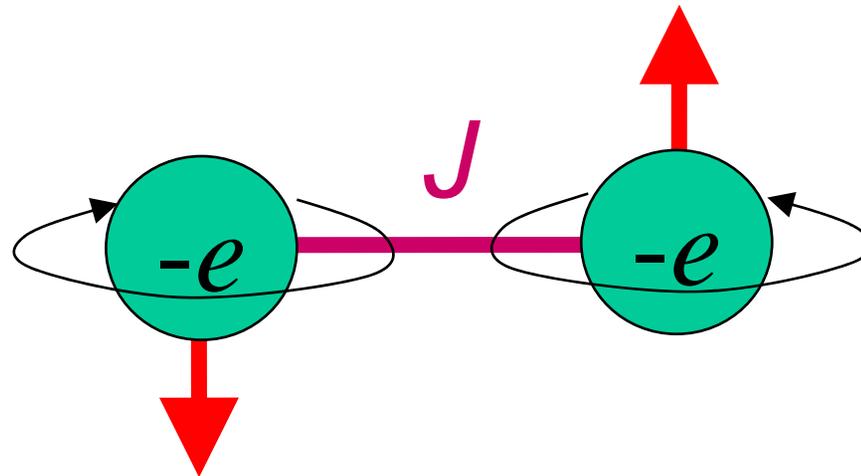
- Full 3D electrical control of spin coherence demonstrated
  - » voltage gating compatible with existing Si technology
- Universal gating possible
  - » with Heisenberg exchange “backbone”
- Future directions
  - » Ferroelectric control of ESR
  - » scaling down to single spin



# Two-qubit gates

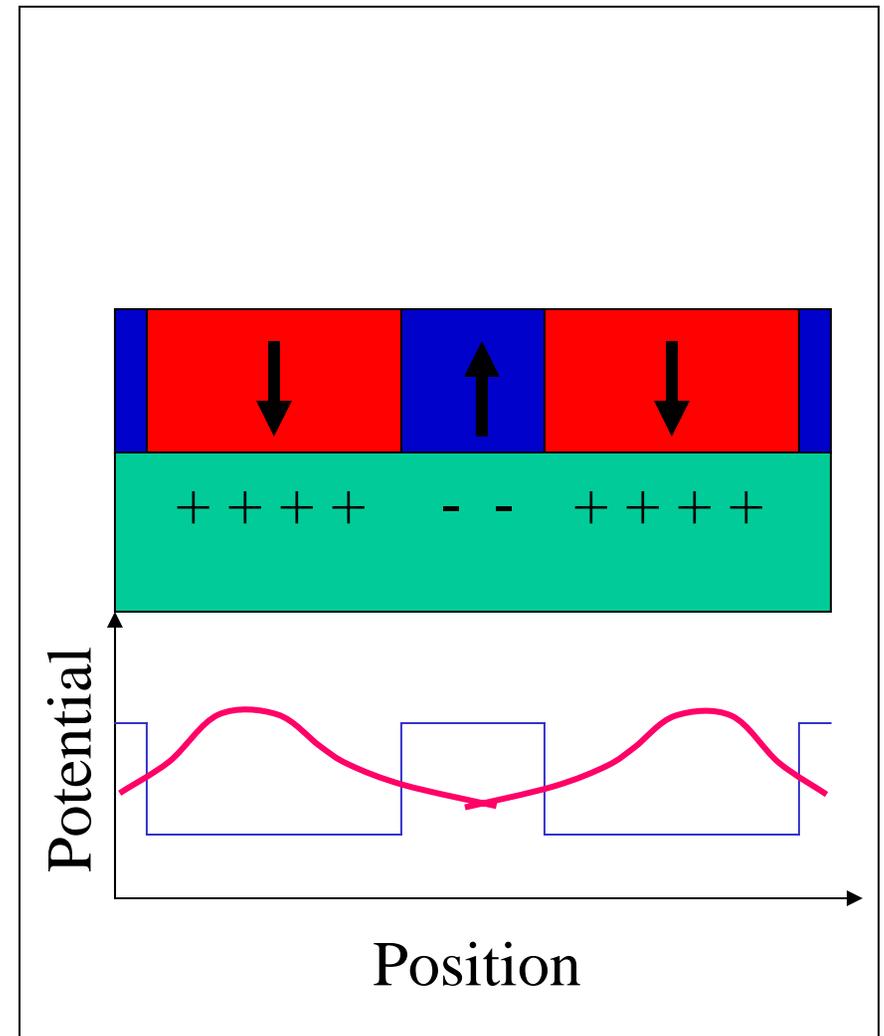
(ferroelectrically controlled spin exchange)

$$H_{ex} = J(\vec{E}) \vec{s}_1 \cdot \vec{s}_2$$



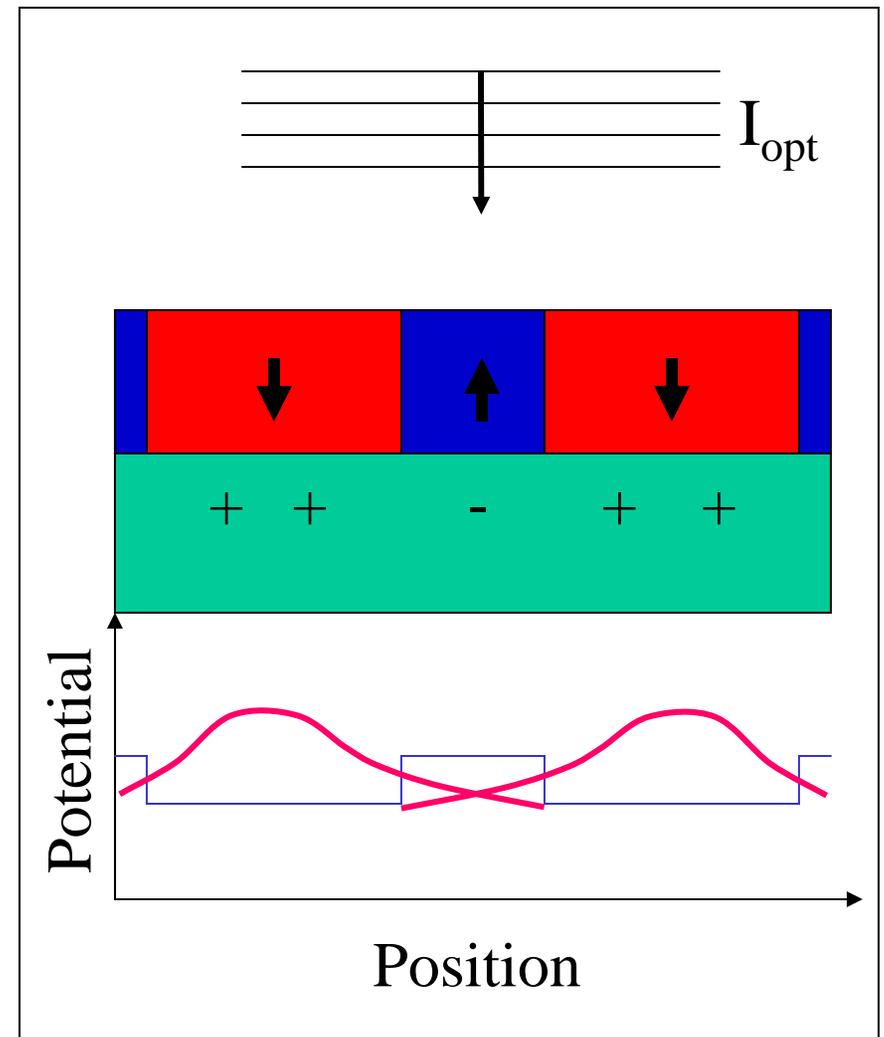
# Optical Rectification and Controlled Exchange

- Optical illumination reduces *magnitude* of ferroelectric polarization
- Tunneling barrier can be modulated optically
  - » With ultrafast lasers 10,000 GHz rates achievable
  - » Can be used to create a universal quantum gate



# Optical Rectification and Controlled Exchange

- Optical illumination reduces *magnitude* of ferroelectric polarization
- Tunneling barrier can be modulated optically
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  - » Can be used to create a universal quantum gate



# Magnitude of Nonlinear Polarization

$$P_{\max}^{(2)} = \left(3.93 \times 10^{11} \text{ e}^-/\text{cm}^2\right) \left(\frac{I_{\text{avg}}}{10 \text{ mW}}\right) \left(\frac{d}{\mu\text{m}}\right)^2 * \left(\frac{76 \text{ MHz}}{\Omega}\right) \left(\frac{r}{1.95 \times 10^{-11} \text{ m/V}}\right) \left(\frac{\tau_{\text{opt}}}{100 \text{ fs}}\right) \left(\frac{n}{2.45}\right)^3$$

$I_{\text{avg}}$  = average laser power     $r$  = electrooptic coefficient

$d$  = spot diameter

$\tau_{\text{opt}}$  = pulse width

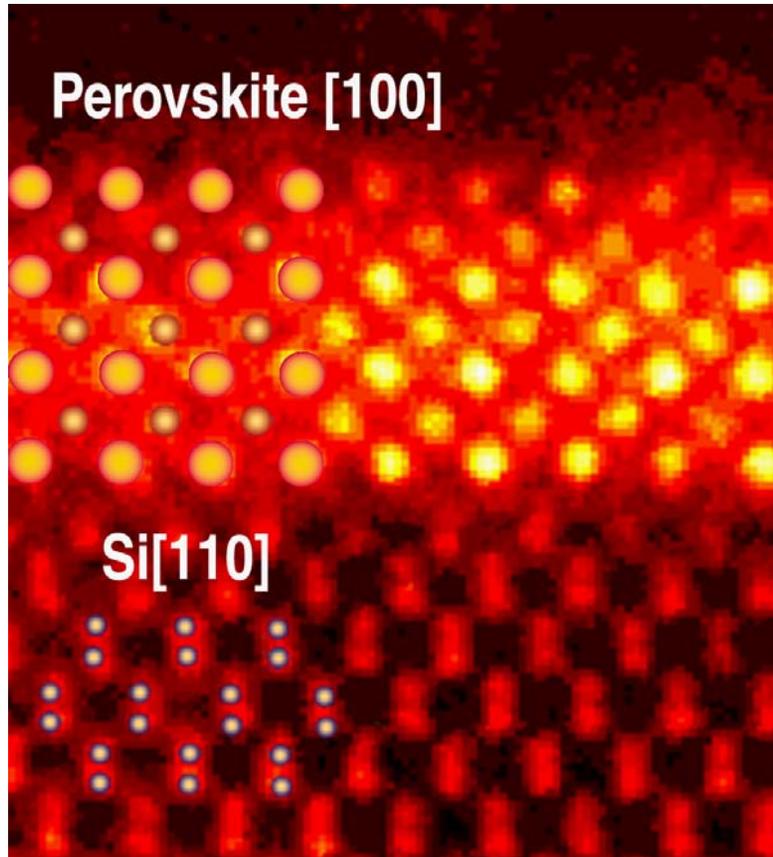
$W$  = repetition rate

$n$  = refractive index

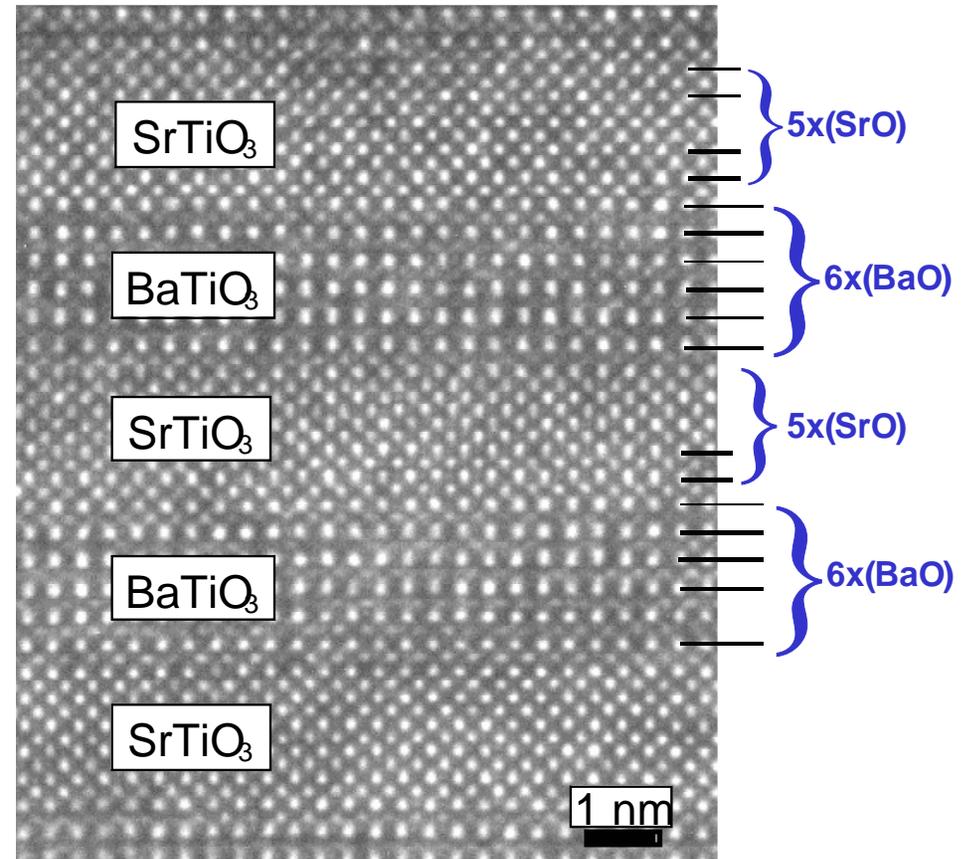


# COSMQC Materials

## Ferroelectric Oxides on Silicon



Rodney McKee, ORNL



Darrell Schlom, Penn State U.



# COSMQC oxides on silicon

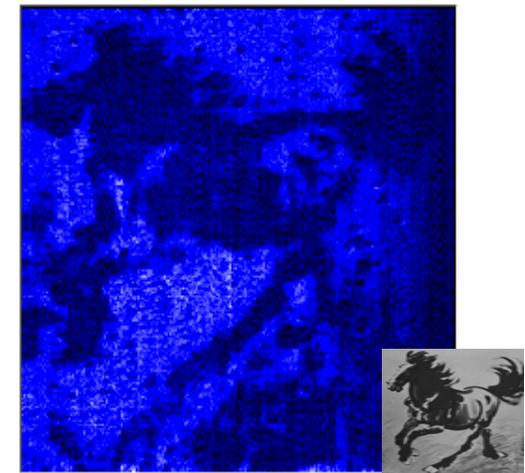
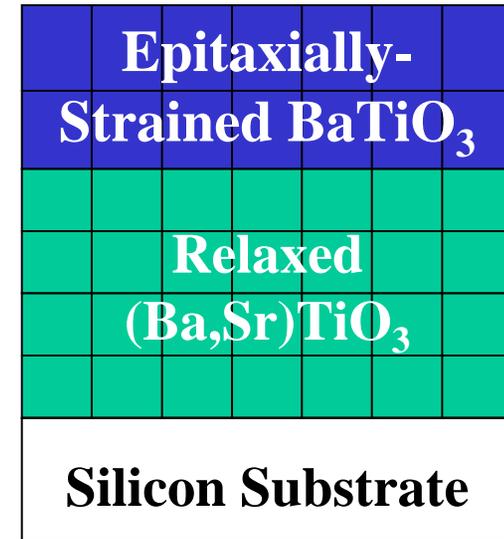
- Requirements for quantum computing architecture
  - » strong ferroelectric field effect for qubit gating
  - » uniform, uniaxial out-of-plane polarization
  - » large electrooptic response for optical rectification
- Two approaches taken so far by Schlom group
  - » commensurate  $\text{SrTiO}_3/\text{Si}$
  - » commensurate  $\text{BaTiO}_3/\text{Relaxed (Ba,Sr)TiO}_3/\text{Si}$



# BaTiO<sub>3</sub> with Out-of-Plane Polarization on Si to Control Spin Interactions

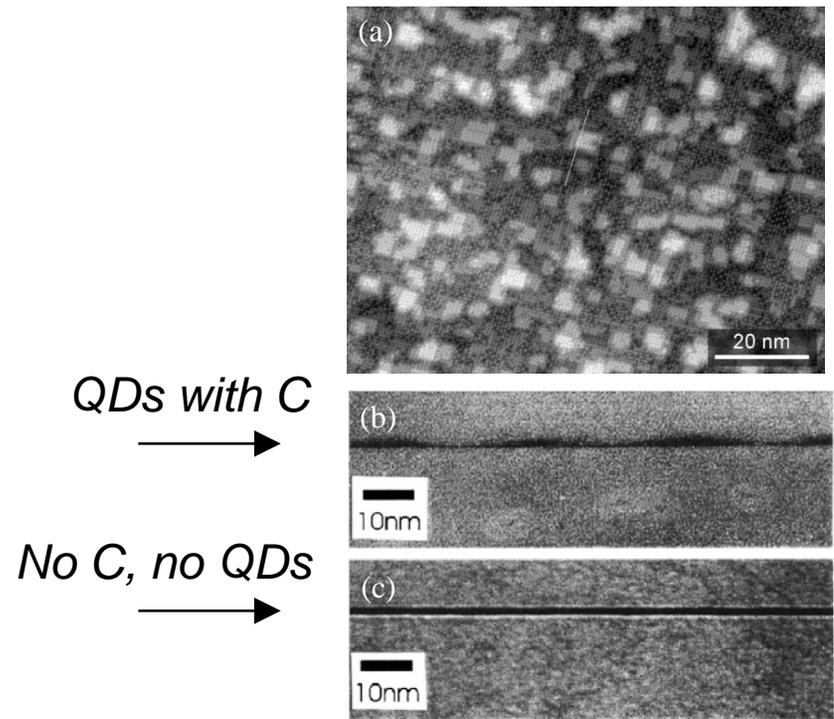
Darrell G. Schlom, Penn State University

- Prior BaTiO<sub>3</sub> / Si Films have all had *In-Plane* Polarization because
  - Large lattice mismatch (3.8%)
  - Large thermal expansion mismatch
- To Achieved Out-of-Plane Polarization in BaTiO<sub>3</sub> / (Ba,Sr)TiO<sub>3</sub> / Si
  - Use epitaxial strain to counteract thermal expansion strain
  - Rocking curve <0.5° for BaTiO<sub>3</sub>
- To Improve Control of Spin Interactions want Thinner (Ba,Sr)TiO<sub>3</sub> Buffer Layer
  - 100 Å works
  - 40 Å does not work so far, but optimizing



# Ge/Si Quantum Dots

- Grow by self-assembly methods
  - » Natural diameter too large ( $d > 20$  nm)
- Direct/indirect crossover occurs near 10 nm
- Smaller QDs nucleate around carbon
  - » Diameters  $< 10$  nm
  - » Strong photoluminescence observed
  - » “directed” self-assembly

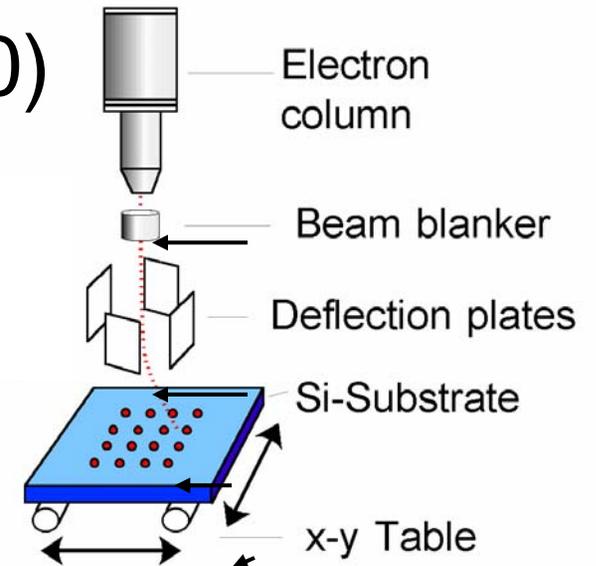
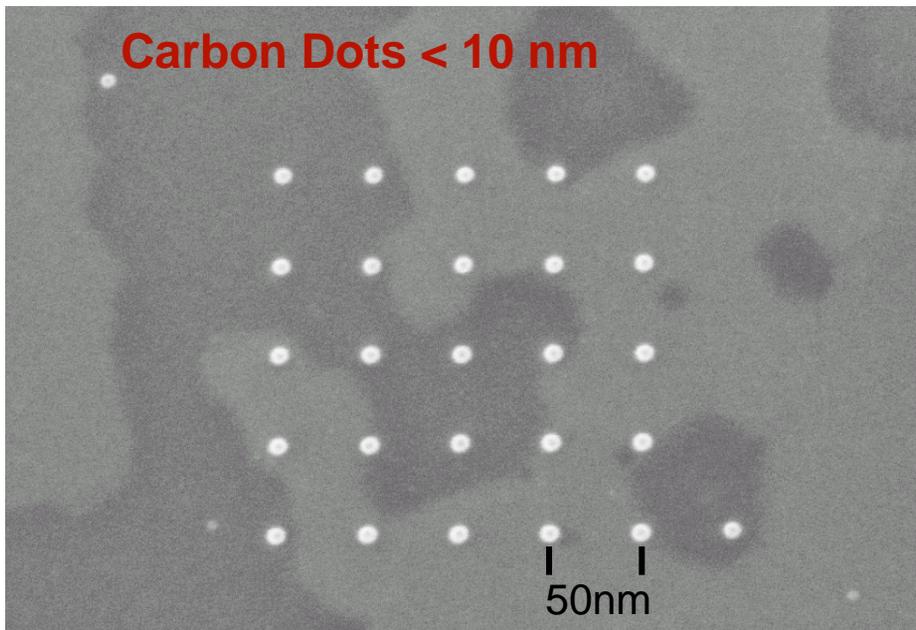


- (a) D. Gruetzmacher, [www1.psi.ch/www\\_lmnh/shine/sigec.htm](http://www1.psi.ch/www_lmnh/shine/sigec.htm)
- (b) (b) X-TEM image of Si-C-Ge quantum dots with 4 ML Ge.
- (c) (c) Same as (b), but without Carbon present, showing absence of QDs. [O. G. Schmidt *et al.*, *Appl. Phys. Lett.* **71**, 2340-2 (1997)].



# Patterning Carbon Dots / Si(100)

**Goal** – To deposit carbon as a template for Ge Quantum Dot Growth

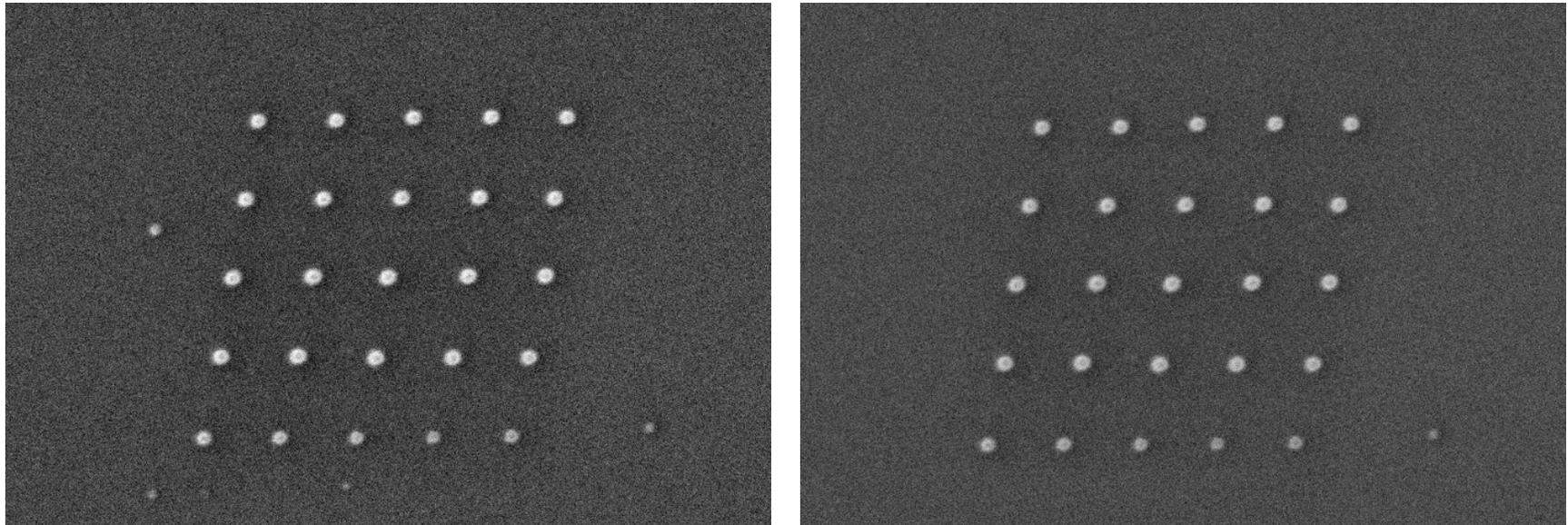


$V_e = 20 \text{ KeV}$   
 Beam Diameter < 1nm  
 Primary beam current ~ 340pA

	<u>Now</u>	<u>Soon</u>
<u>Field of play:</u>	50 $\mu\text{m}$ x 50 $\mu\text{m}$	2mm x 2mm
<u>Max. # dots:</u>	~ 10 <sup>5</sup>	~ 10 <sup>8</sup>
<u>Time:</u>	~10 <sup>5</sup> seconds i.e. ~27h	~ 10 <sup>3</sup> seconds i.e. < 20min.



# Thermal Properties of Patterned C-Dots



Annealing at 1300K (30") – no change

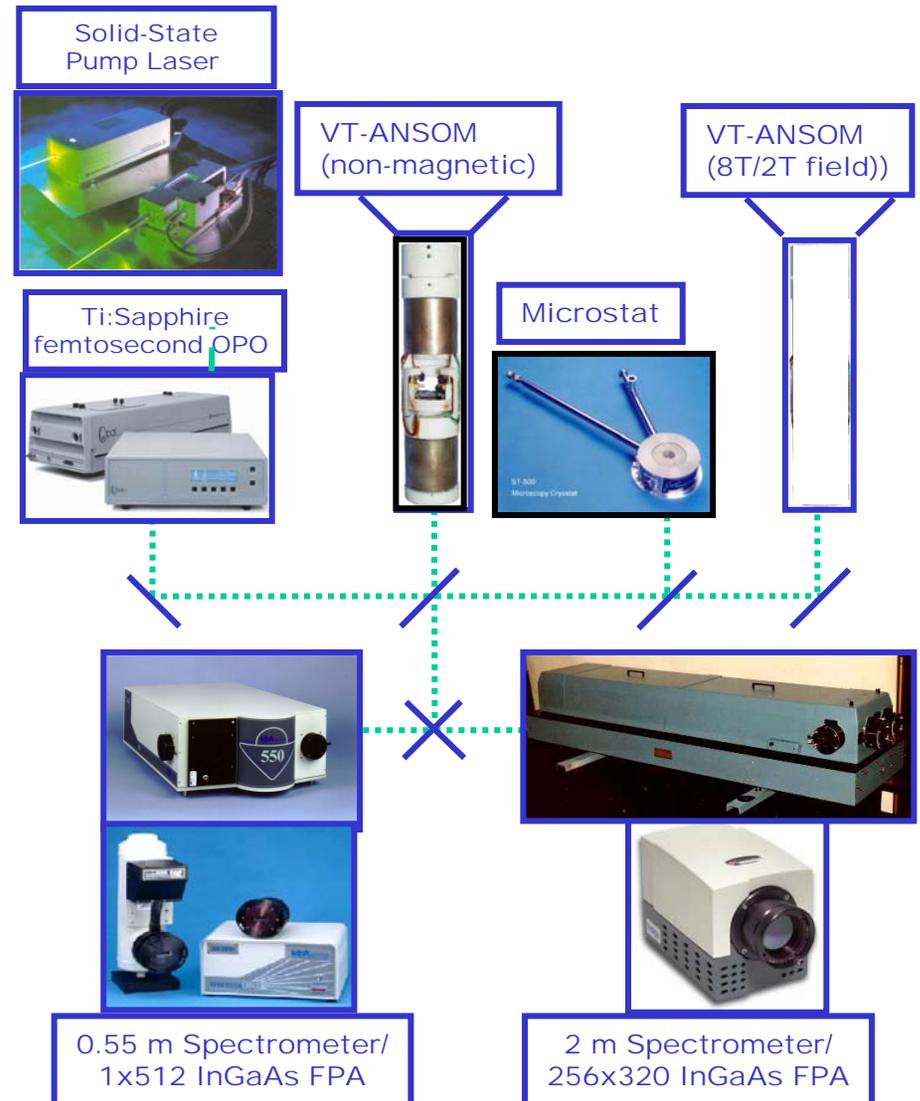


300nm

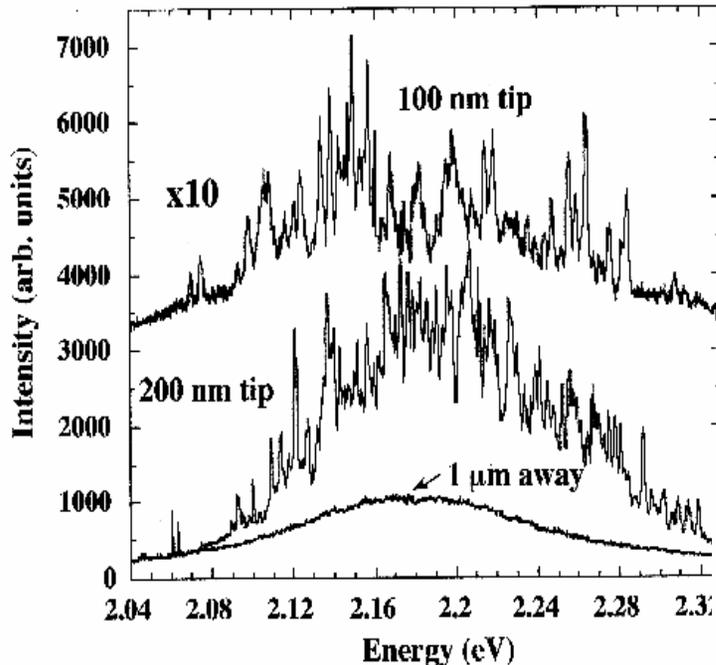


# Optical and Scanning Probes of Ferroelectric/Semiconductor Heterostructures

- Apertureless NSOM (ANSOM)
- Ti:Sapphire → OPO (1 μm-2 μm)
- Three cryostats
  - » Microcryostat for photoluminescence (PL), Kerr microscopy
  - » Non-magnetic for ANSOM
  - » Vector field (8T/2T) for ANSOM, transport
- Two spectrometers
  - » 0.55 meter spectrometer with cooled InGaAs array for PL
  - » 2.0 meter spectrometer with 2D focal plane array for spectrally resolved Kerr rotation



# Coherent Spin Dynamics of a Single Quantum Dot: Background

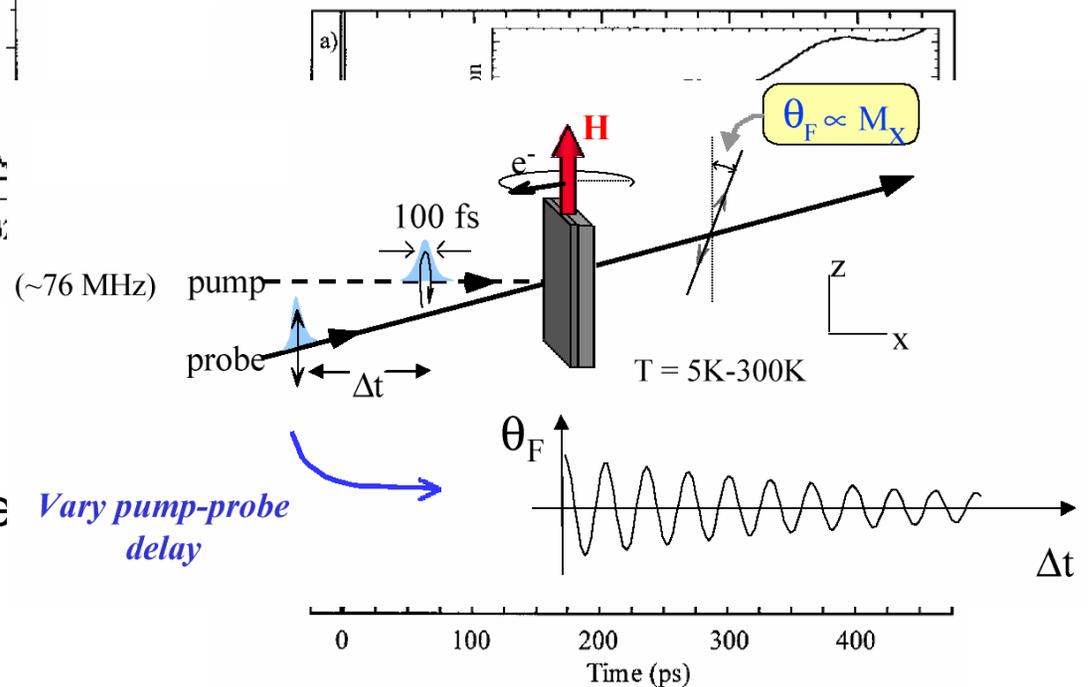


Flack *et al.*, PRB **54**, R17312-15 (1996).

Previous investigations of quantum dot spin coherence probed large numbers of quantum dots...

Photoluminescence spectroscopy combines spatial and spectral resolution, but does not probe spin coherence

## Time-resolved Faraday Rotation



Gupta *et al.*, PRB **59**, R10421 (1999).



# Our Approach

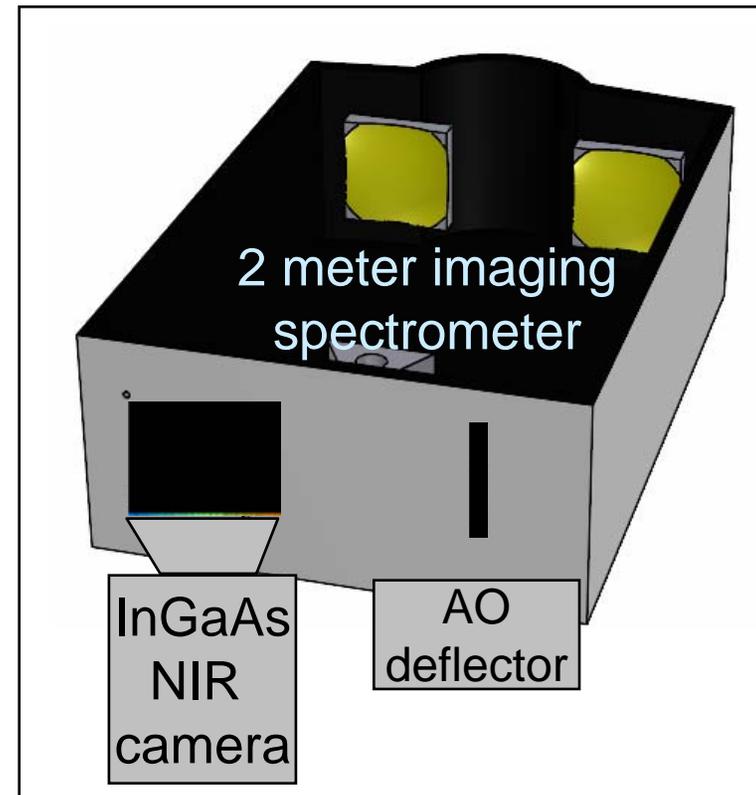
Combine high spatial and spectral resolution to measure coherent spin dynamics in single quantum dots

## Spatial Resolution



Variable-temperature Apertureless NSOM

## Spectral Resolution



Lock-in Optical Spectrometer

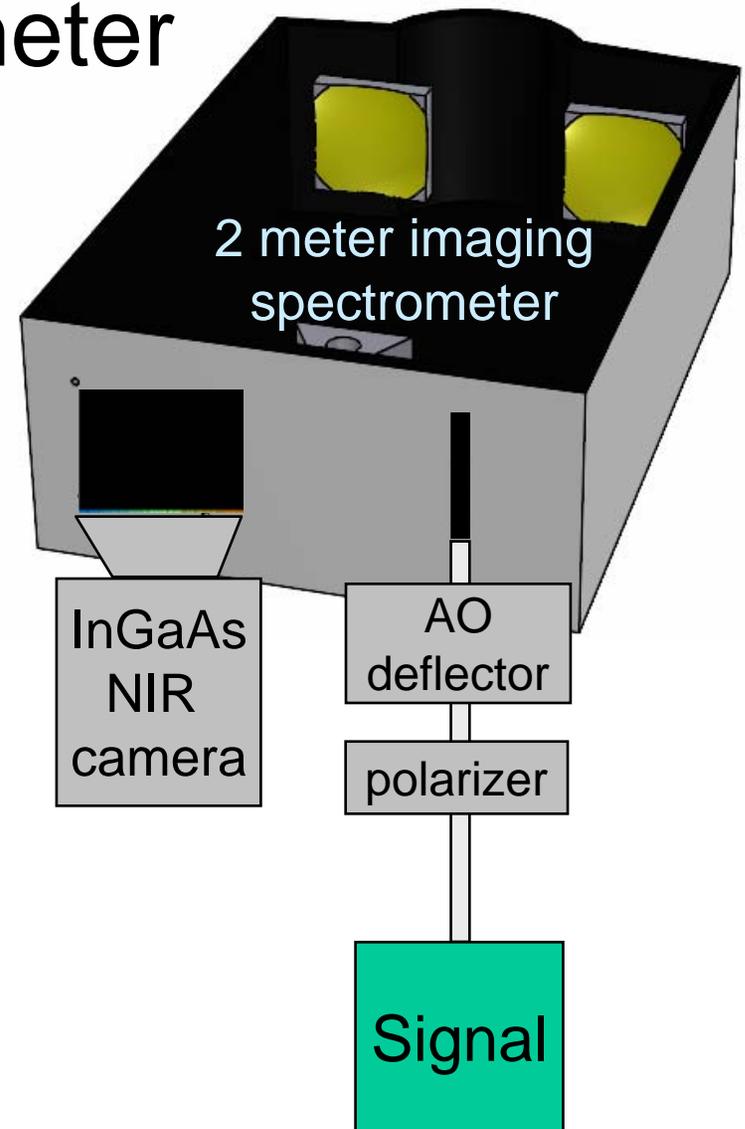
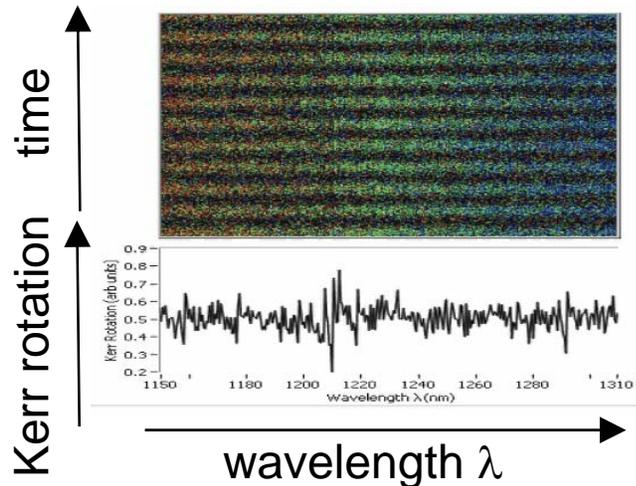


# Lock-in Spectrometer

- Goal: spectroscopy of single quantum dots
  - » time-resolved absorption
  - » time-resolved Kerr rotation of single spins
- Challenge: achieving necessary SNR
  - » Photon number fluctuations dominant source of noise
  - » Need an array of large-area detectors with lock-in amplifiers!

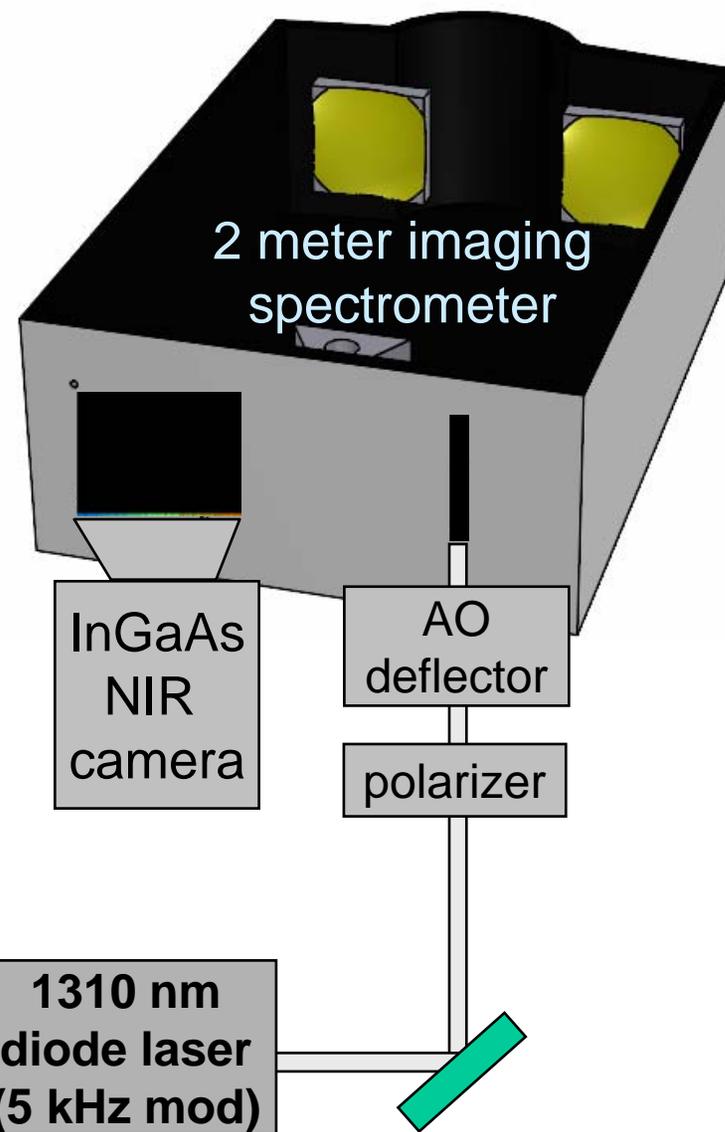
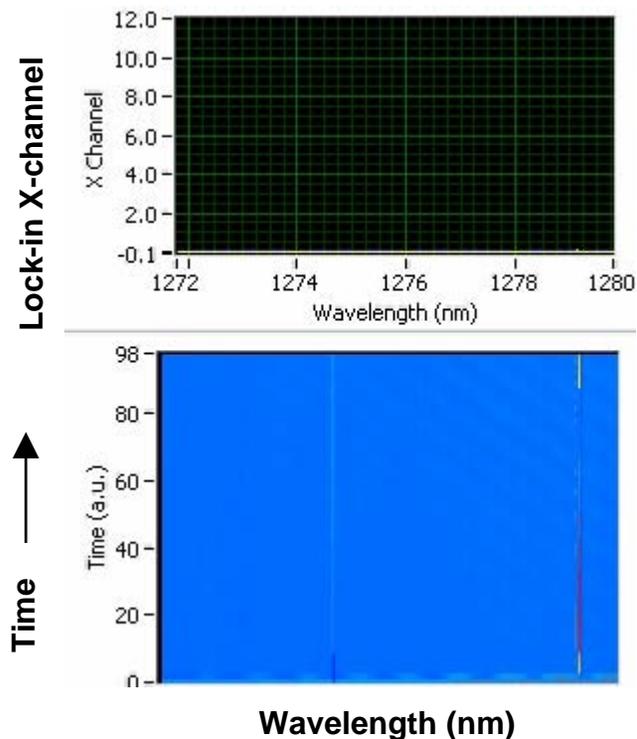
80 Mbytes/sec

Real-time DSP



# Lock-in Optical Spectrometer: First Test

“Sample”: 1310 nm diode laser



Number of channels	320x2=640
Spectral bandwidth @1300nm	5 meV
Spectral resolution	<50 $\mu\text{eV}$
Noise-equivalent power	< $5 \times 10^{-12}$ W/cm <sup>2</sup>

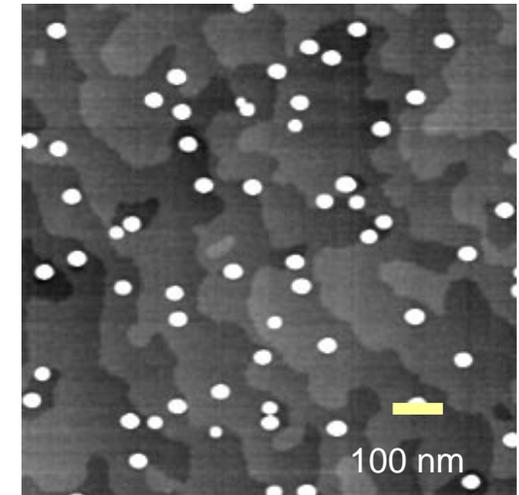
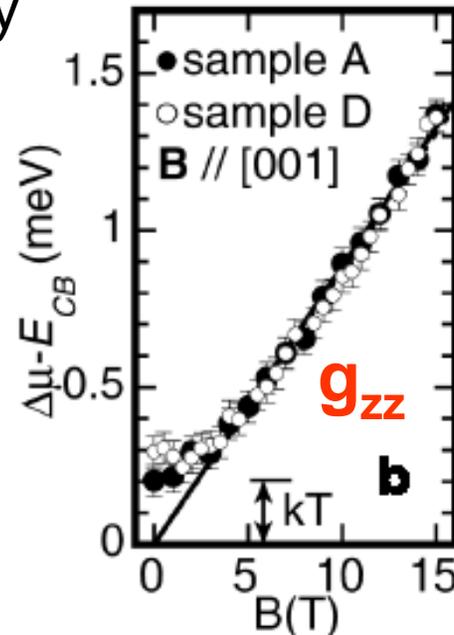
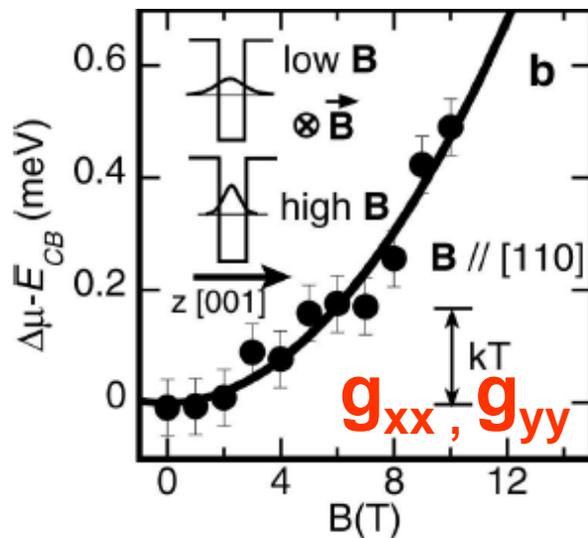


# InAs:GaAs Quantum Dots

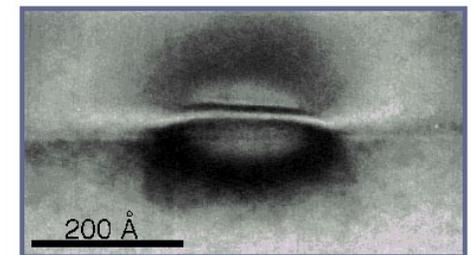
G. Medeiros-Ribeiro

Laboratório Nacional de Luz Síncrotron, Campinas, Brazil

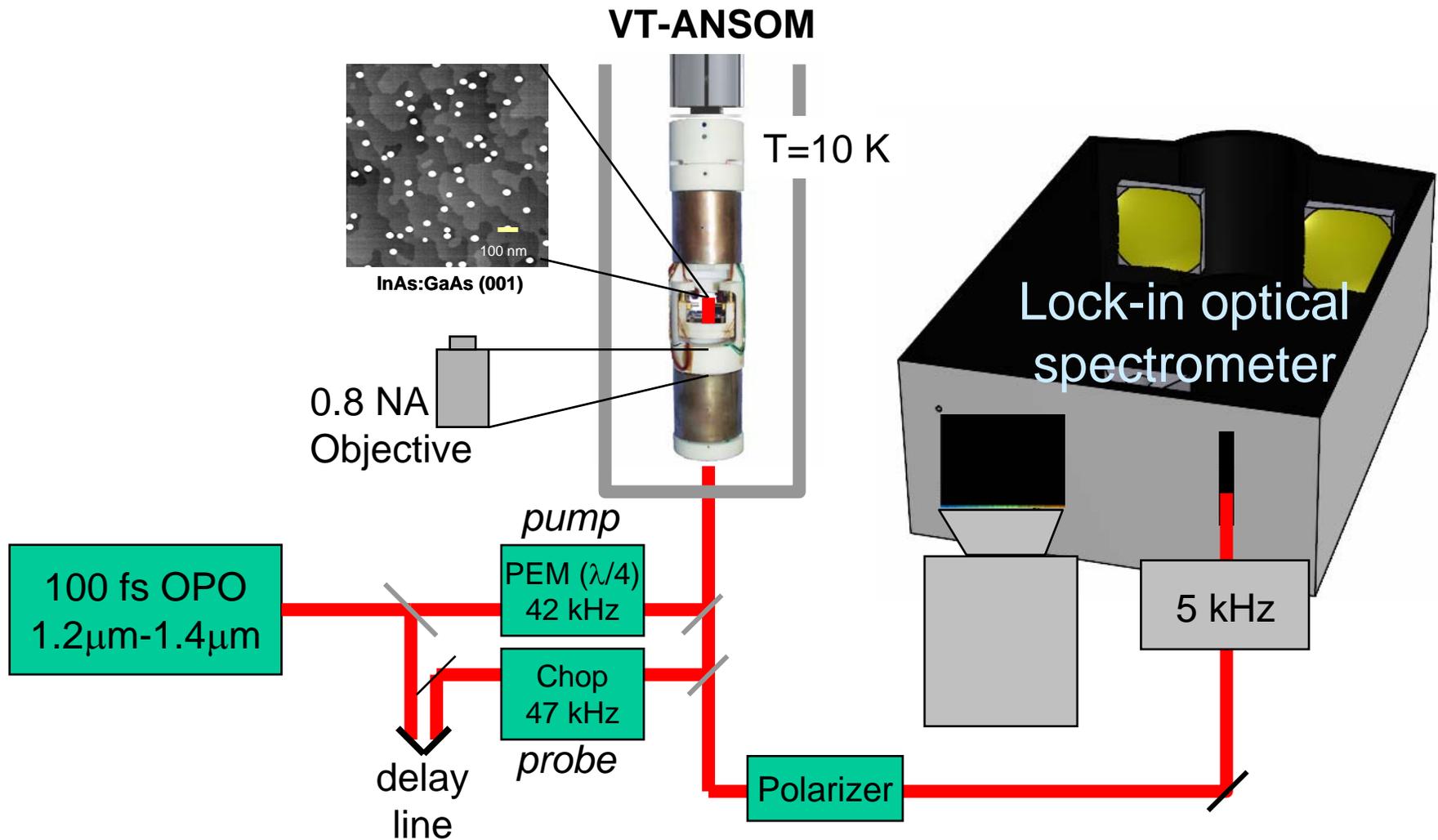
- Interband absorption energies comparable to Ge quantum dots
  - » 950 meV-1 eV,  $\lambda=1.25-1.3\mu\text{m}$
  - » Density  $10^8\text{ cm}^{-2} \rightarrow \sim 100\text{ dots}/\mu\text{m}^2$
- Large g-tensor anisotropy



InAs:GaAs (001)



# Experiment in Progress...



# Summary

- Quantum computation presents many materials, experimental and theoretical challenges
- New device applications for ferroelectric/semiconductor heterostructures

